

Hopping and clustering of oxygen vacancies in $\text{BaTiO}_{3-\delta}$ and the influence of the dynamically disordered off-centred Ti atoms

Francesco Cordero

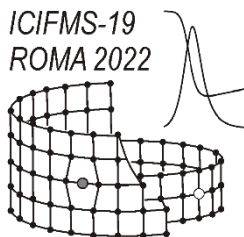
CNR-ISM, Istituto di Struttura della Materia
Area della Ricerca di Roma-Tor Vergata, Roma, Italy

Francesco Trequattrini

Dip. Fisica, Università di Roma "La Sapienza", Roma, Italy

David A. B. Quiroga, Paulo Sergio da Silva Jr.

Dep. Fisica, Universidade Federal de São Carlos,
São Carlos, Brazil

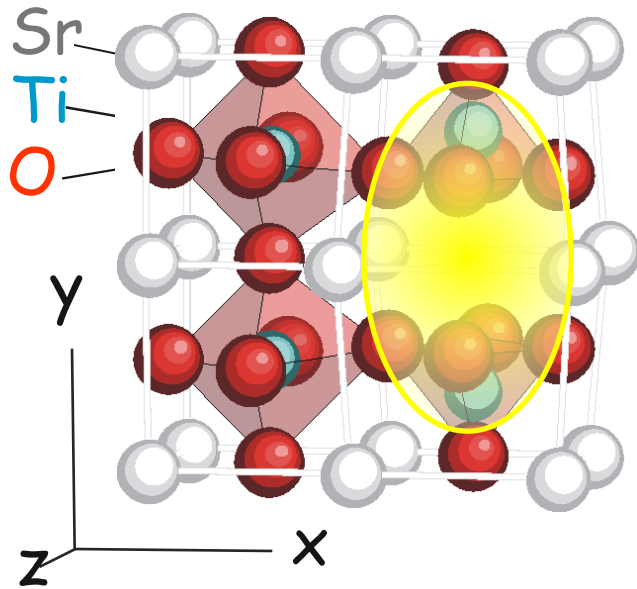


ICIFMS-19 (Rome, 2022)

Summary

- brief introduction on O vacancies in perovskites
- anelastic spectra of $\text{SrTiO}_{3-\delta}$: free, paired and aggregated V_O
- anelastic spectra of $\text{BaTiO}_{3-\delta}$: similar but
- the barrier for the hopping of an isolated V_O is larger and decreases with increasing δ
- the anisotropy of the elastic dipole is three times larger
- simple explanation in terms of Ti dynamically off-centred over 8 positions also in the cubic phase

Perovskite cubic structure and O vacancies



formula: ABX_3 , e.g. $SrTiO_3$

high T: cubic structure;

low T: distortions and rotations of the O octahedra and cation off-centering

variety of properties: ferroelectricity, giant magnetoresistance, ionic conductivity, superconductivity

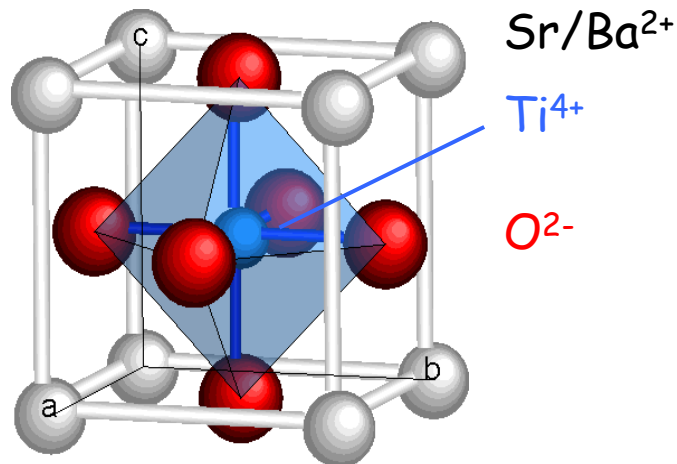
O vacancy in undoped cubic perovskite:

only elastic dipole $\rightarrow$ anelastic but not dielectric relaxation

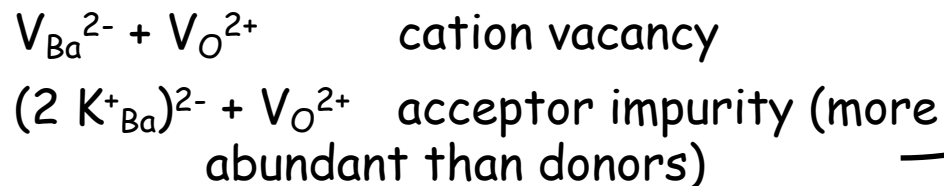
$$\lambda^{(v)} = \begin{pmatrix} \lambda_1 & 0 & 0 \\ 0 & \lambda_2 & 0 \\ 0 & 0 & \lambda_1 \end{pmatrix}$$

$$\Delta\lambda = \lambda_2 - \lambda_1$$

Defects and compensating O vacancies



in a purely ionic picture the defects are charge compensated:

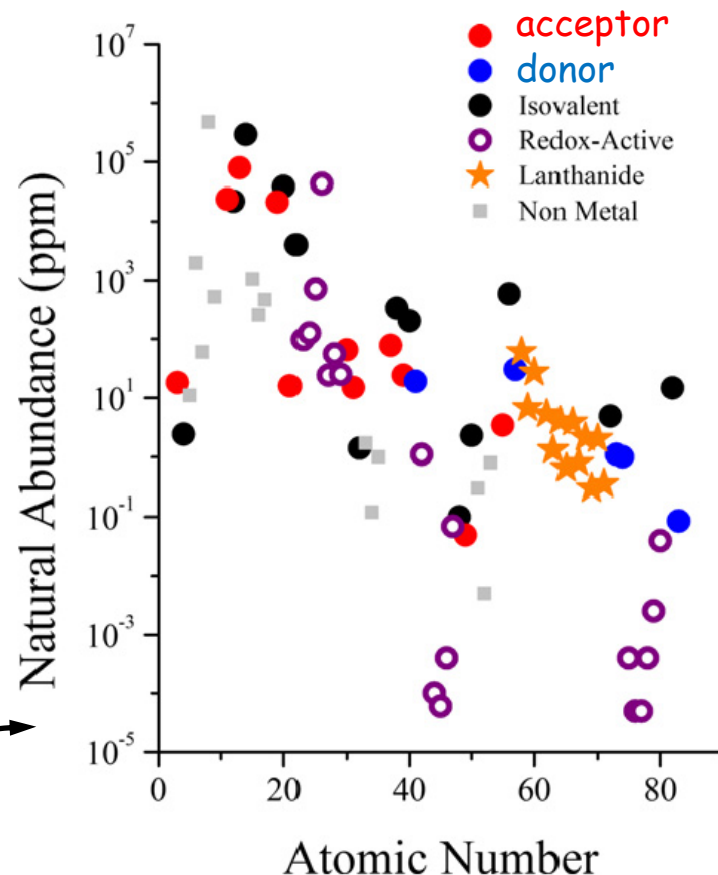


the ionic picture is a schematization:

- the bonds are partially covalent
- V_O may have charge 2+, 1+, 0

V_O may be introduced in a stoichiometric material by heating in an O free or reducing atmosphere ($CO + O \rightarrow CO_2 + V_O$ or $H_2 + O \rightarrow H_2O + V_O$)

↑ sample surface ↓ goes into the bulk



Maier and Randall
 J. Am. Ceram. Soc., 99 3360 (2016)

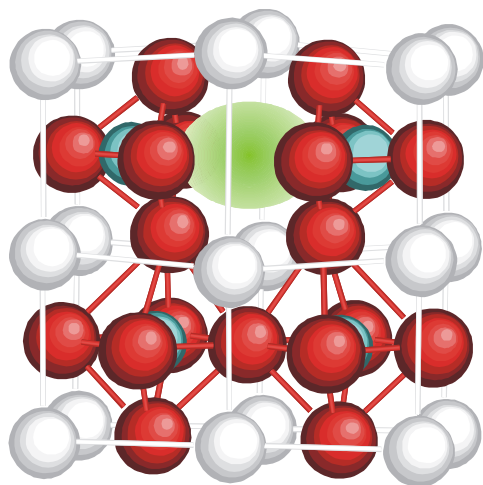
Importance of O vacancies in perovskites

Ionic conductors (e.g. $\text{BaCe}_{1-x}\text{Y}_x\text{O}_{3-x/2}$): V_{O} and H are the charge carriers

High- T_c superconductors (e.g. $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$): doping depends on the concentration and ordering of O in non-stoichiometric planes

ferroelectrics (e.g. $\text{PbZr}_{1-x}\text{Ti}_x\text{O}_3$): V_{O} are considered responsible for aging and fatigue

Elastic dipole of an O vacancy (calculations)



Calculations of atomic displacements around V_O

C.H. Park and D.J. Chadi, Phys. Rev. B **57**, R13961 (1998)

small outward shifts of nn Pb and Ti and inward shifts of nn O (electrostatic interaction)

Buban *et al.*, PRB **69**, 180102 (2004)

larger and longer range atomic displacements with larger supercell size

The elastic dipole of an O vacancy in a perfect perovskite lattice might be very small and nearly isotropic

D. A. Freedman *et al.*, Phys. Rev. B **80**, 064108 (2009)

V_O^{2+} in $SrTiO_3$: $Tr(\lambda) = 0.0039$ $\Delta\lambda = \cancel{0.41} (= 18 \Delta\lambda_{mea})$

E.J. Granhed *et al.*, J. Mater. Chem. A **7**, 16211 (2019)

$V_O^{\times}$ in $BaTiO_{3-x}H_x$: $Tr(\lambda) = -0.049$ $\Delta\lambda = 0.067 (= 0.87 \Delta\lambda_{mea})$

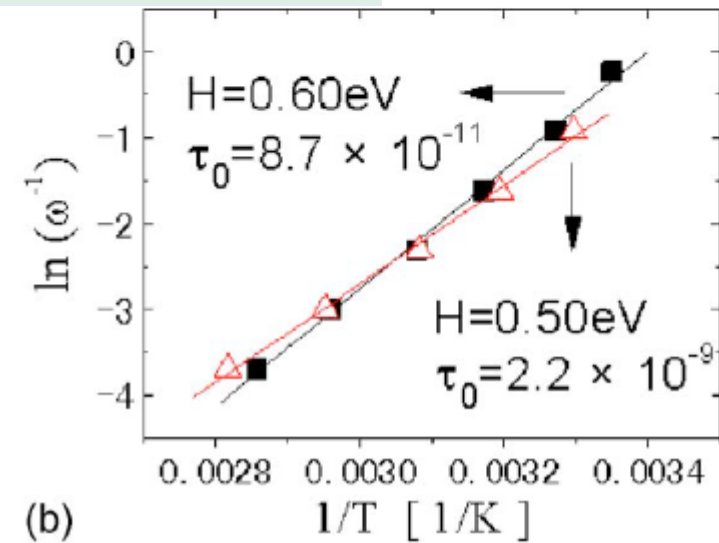
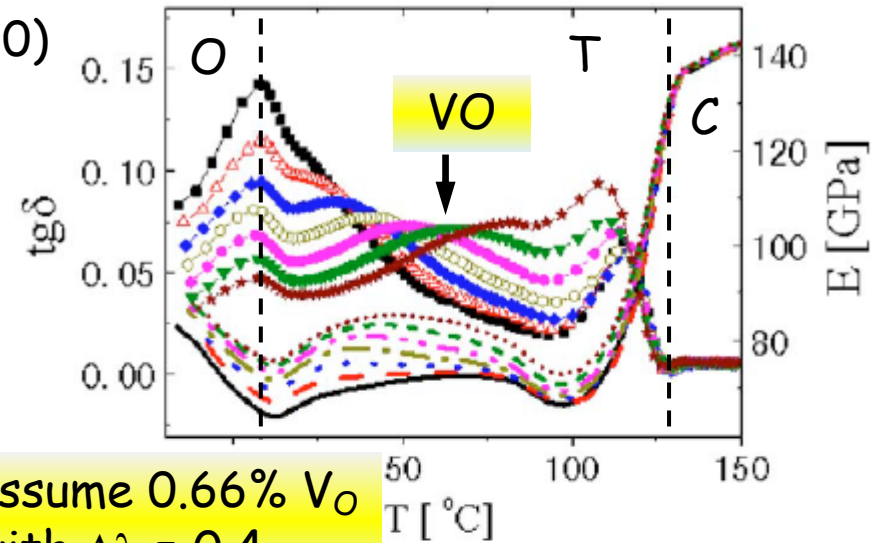
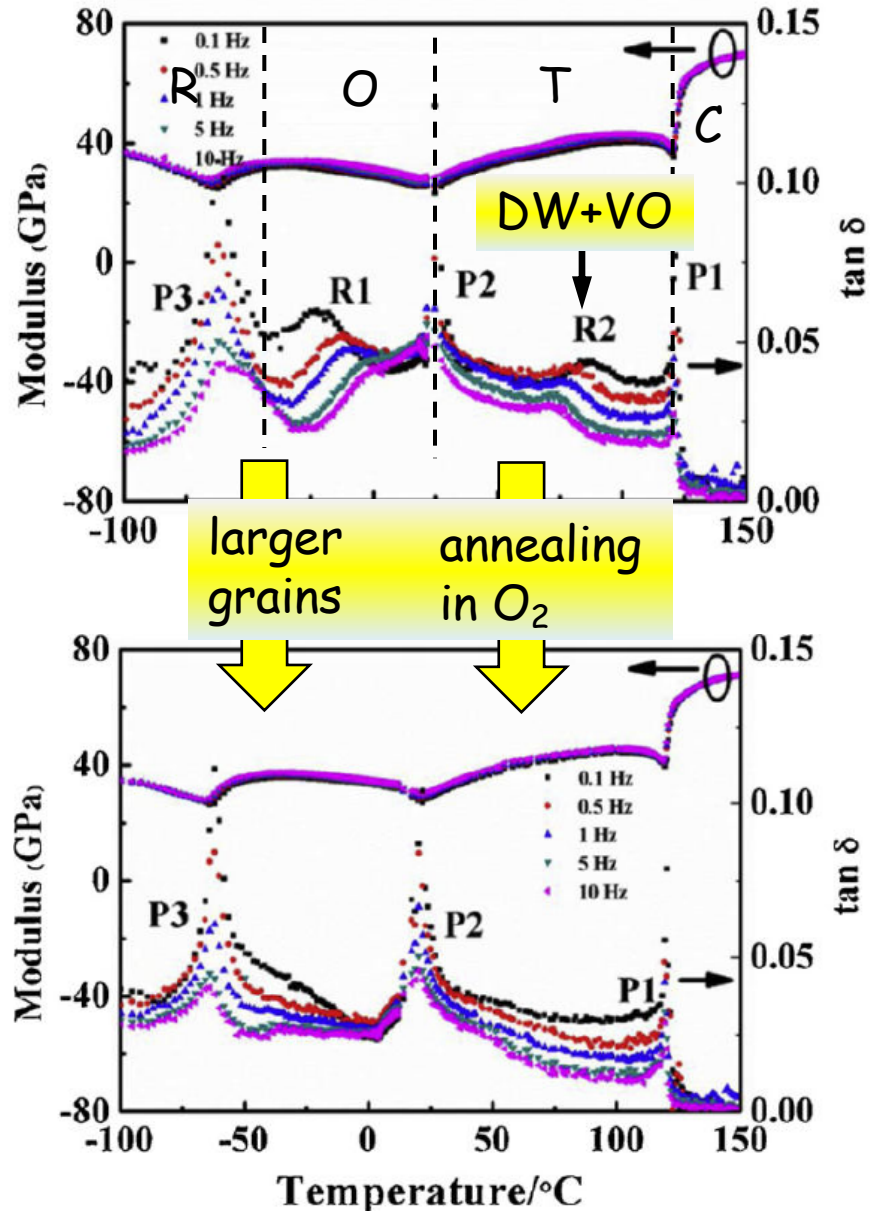
F. Cordero
PRB **76**, 172106 (2007)

anelastic
relaxation

F. Cordero *et al.*
Jalcom **874**, 159753 (2021)

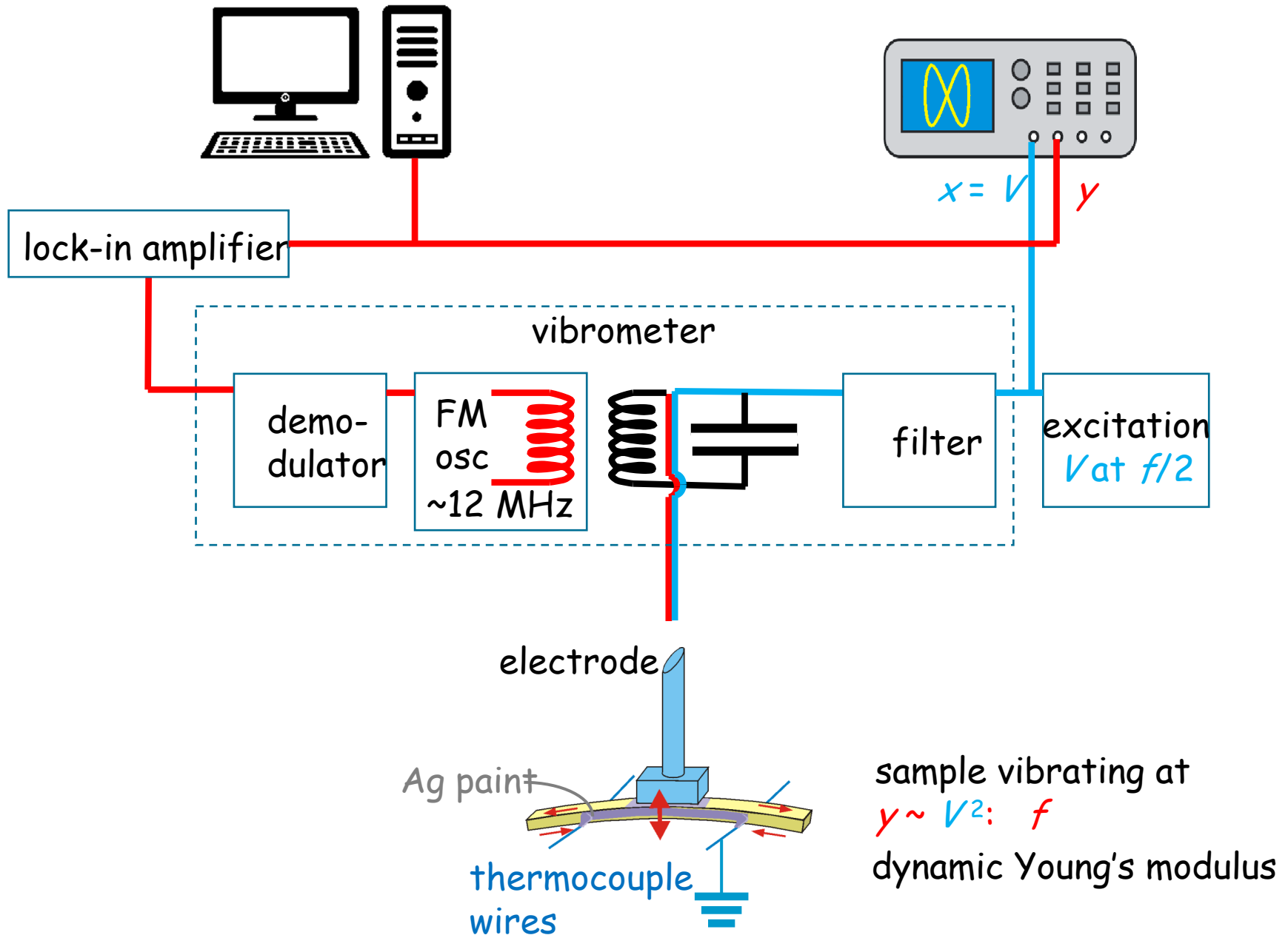
Ceramic $\text{BaTiO}_{3-\delta}$ - previous anelastic measurements

Y. Chen *et al.* J. Eur. Ceram. Soc. 40 391 (2020)



Chen *et al.* Appl. Phys. Lett. 89, 071916 (2006)

Anelastic measurements - free flexural resonance



Experimental - samples

ceramic BaTiO_3

preparation in UFSCar, São Carlos

bar sintered at 1350 °C for 2 h

93.6% of the theoretical density

cut into two bars $42 \times 6.3 \times 0.68 \text{ mm}^3$

Young's modulus, 1st and 3rd flexural modes (2.2 and 12 kHz)

F. Cordero, F. Trequattrini, D.A.B. Quiroga, P.S. Silva Jr.

J. Alloys and Compounds 874 159753 (2021) Special Issue ICIFMS-19

single crystal SrTiO_3

sample: bar $26 \times 3.4 \times 0.5 \text{ mm}^3$ from wafer of M.T.I. Corporation; edges || $\langle 100 \rangle$

complex compliance s_{11} , 1st and 5th flexural modes (5.5 and 74 kHz)

F. Cordero, Phys. Rev. B 76, 172106 (2007)

F. Cordero, Mater. Sci. Engin. A 521-522 77 (2009) - ICIFMS-15

Experimental - sample reduction

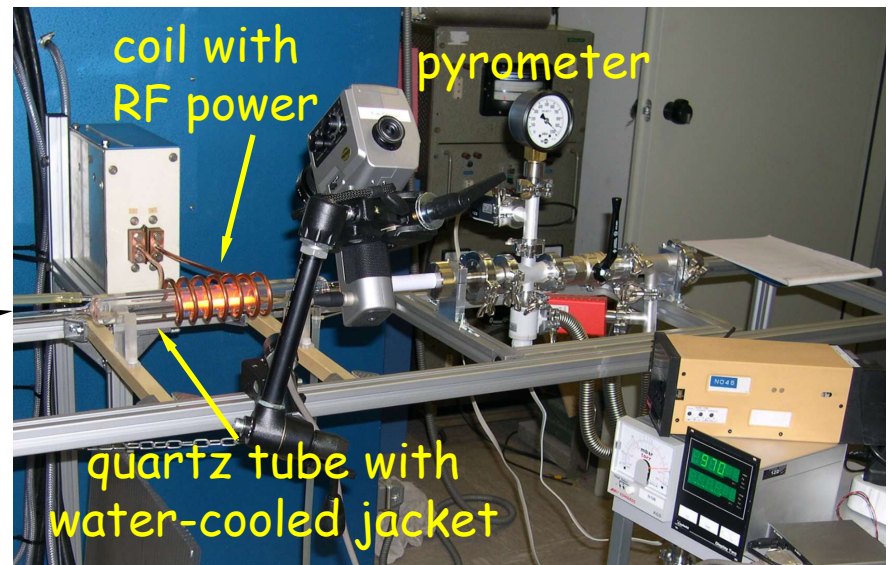
Induction heating at 900-1250 °C for 0.5-3 h in CO/O₂ flux
+ homogeneization 800 °C for 1 h

sample inserted in Pt holder



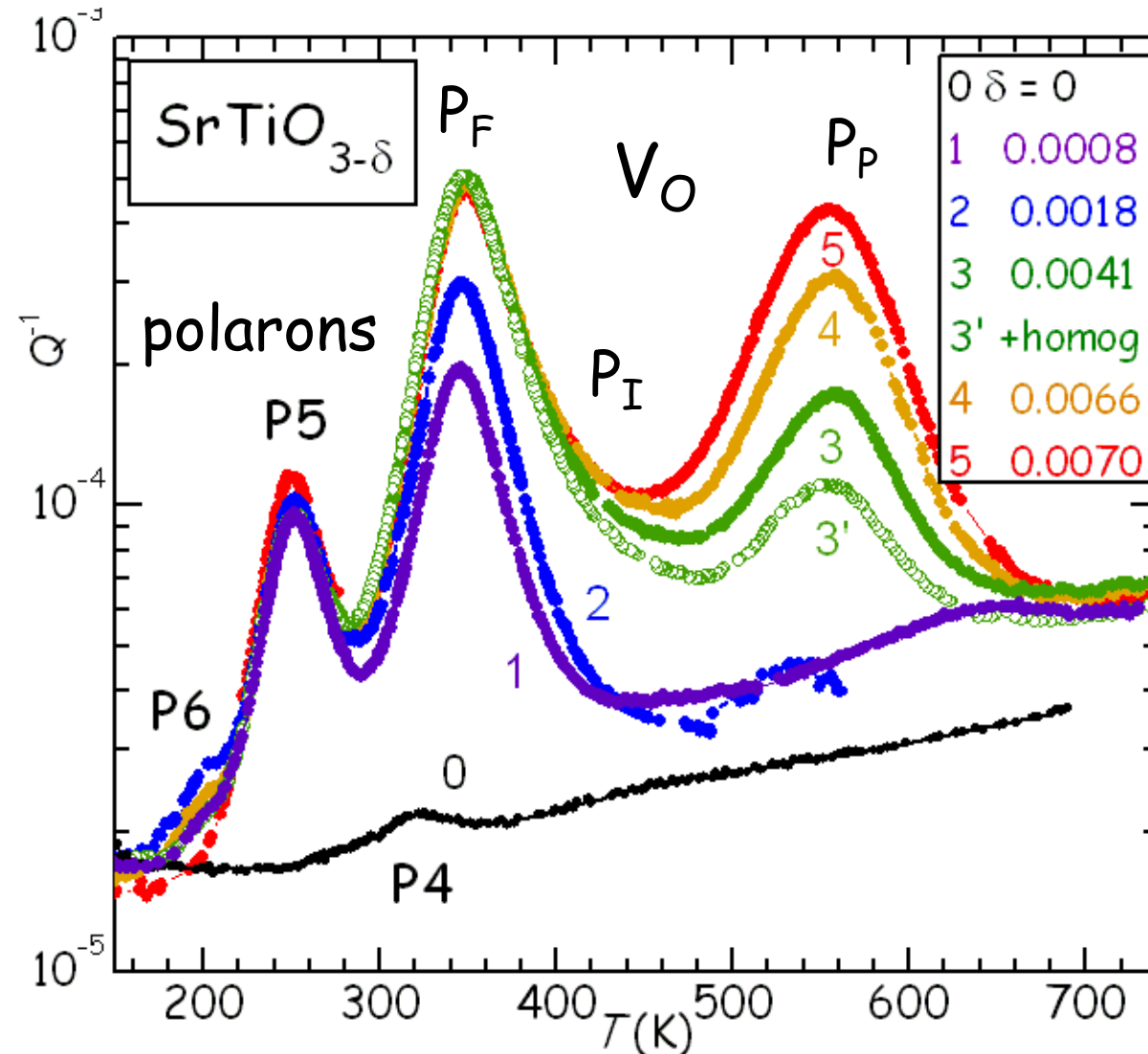
no anelastic relaxation peak appearing
after reduction can be due to H

flow of ~1000 mbar
0.1CO + 0.9Ar or O₂



- O stoichiometry:
- mass change after reduction and reoxygenation
 - temperature of the structural phase transition

Anelastic spectrum vs x

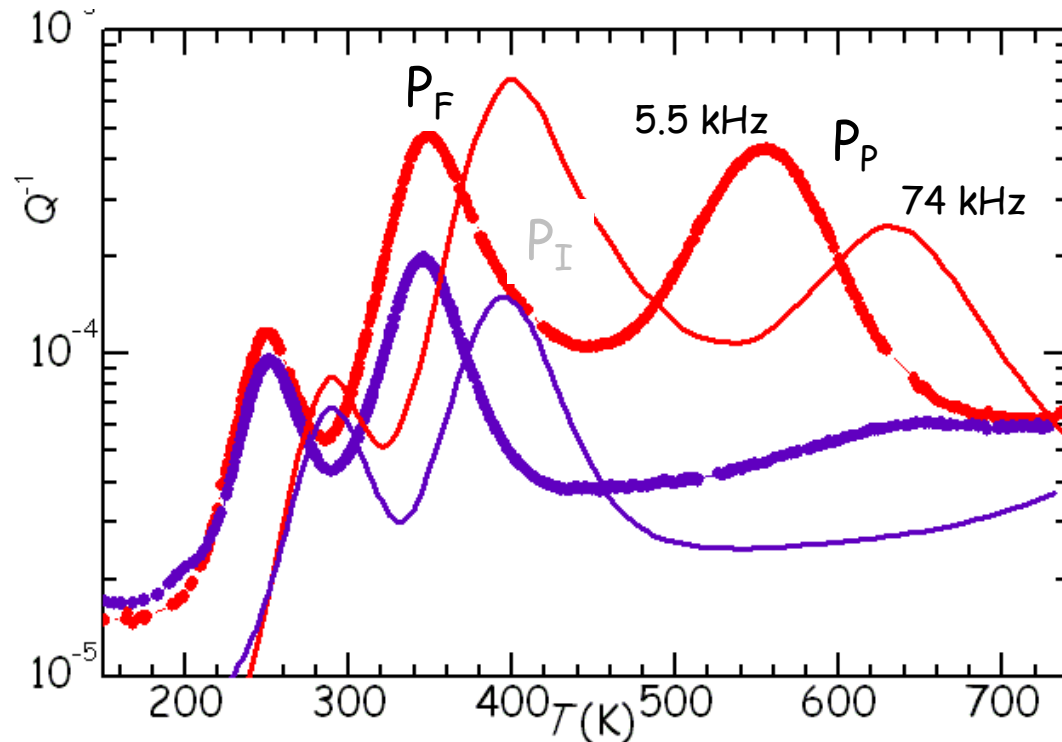


The creation of V_O introduces five peaks:

P_F-P_P grow considerably with increasing δ and therefore are due to V_O

P₅ saturates already at $\delta = 0.001$ and has a low activation energy: polarons?

Explanation of P1-P3 in terms of free and paired V_O



P_F : free V_O $\Delta(T) \propto c_f / T$

at low δ only $c_f \sim \delta$

P_P is absent

P_F decreases as $1/T$

at high δ $c_f = \delta - 2c_p$

pairs dissociation $\rightarrow$

$c_p(T)$ is a decreasing function

$c_f(T)$ is an increasing function

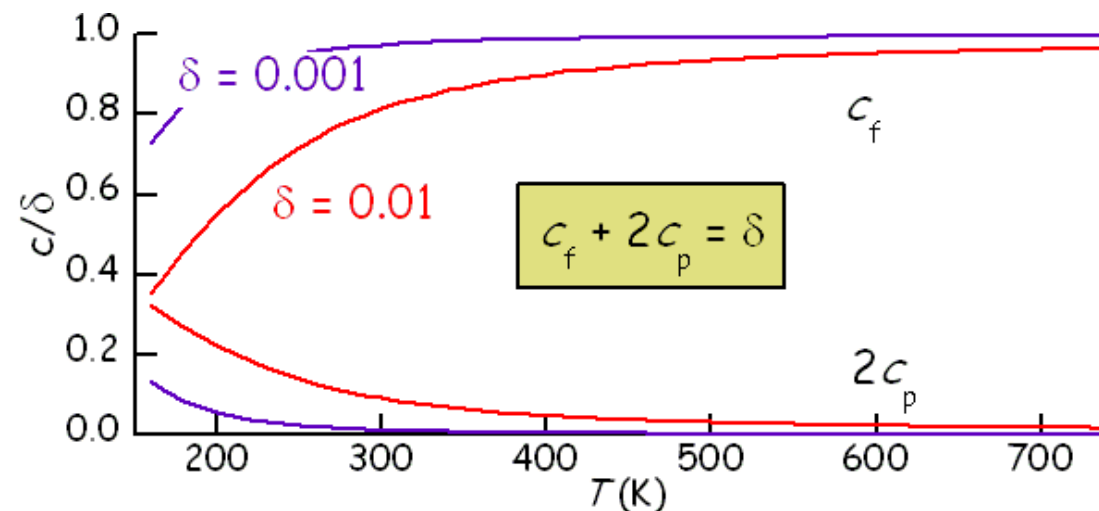
P_P : paired V_O $\Delta(T) \propto c_p / T$

$c_p(T)$ is a decreasing function

the intensity decreases

faster than $1/T$

P_I : intermediate step of pair reorientation + other jumps



Statistical model for aggregated V_O

Subdivide the crystal into clusters of cells that are small enough to write their grandpartition function Z with all the possible configurations of V_O

$$(1) \quad Z = \sum_{\alpha} w_{\alpha} = \sum_{\alpha} m_{\alpha} \exp\left(\frac{n_{\alpha}\mu - E_{\alpha}}{kT}\right) \quad (2) \quad \mu: \quad \frac{kT}{Z} \frac{\partial Z}{\partial \mu} = \frac{\sum_{\alpha} n_{\alpha} w_{\alpha}}{\sum_{\alpha} w_{\alpha}} = \sum_{\alpha} \bar{n}_{\alpha} = \delta$$

n_{α} occupation number of α -th configuration

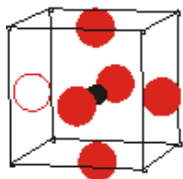
m_{α} multiplicity

E_{α} energy

w_{α} statistical weight

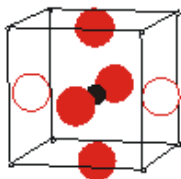
μ chemical potential from the implicit equation (2)

$$E_f = 0$$



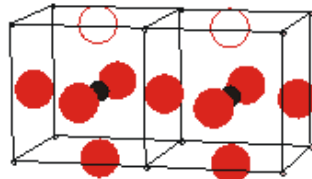
isolated
(free)

$$E_p < 0$$

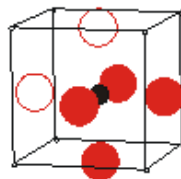


stable pairs

$$E_p$$

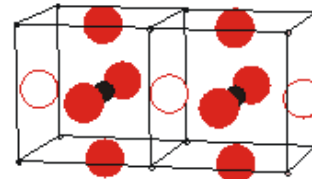


$$E_{nn} > E_p$$



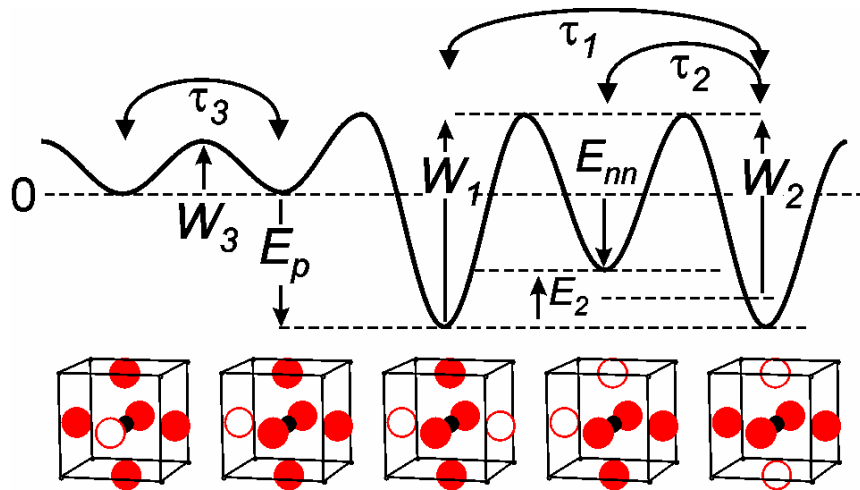
nearest
neighbours
pair

$$E_p + E_c$$



chain

Anelastic relaxation



parameters:

W_1 = barrier for free hopping

W_3 = barrier for pair reorientation

W_2 = barrier for intermediate step

E_p = pair binding energy

E_c = binding of additional V into a chain

τ_0 = preexponential factors

α = Fuoss-Kirkwood broadening

$\Delta\lambda$ = change of elastic dipole for isolated V

$(\Delta\lambda)_1 \approx 2\Delta\lambda =$ " for pair reorientation

Three relaxations corresponding to P_F , P_P and P_I :

$$Q^{-1} = \frac{2}{9} \frac{c\nu_0}{s_{11}k_B T} (\Delta\lambda)^2 \frac{\alpha(\omega\tau)^\alpha}{1 + (\omega\tau)^{2\alpha}}$$

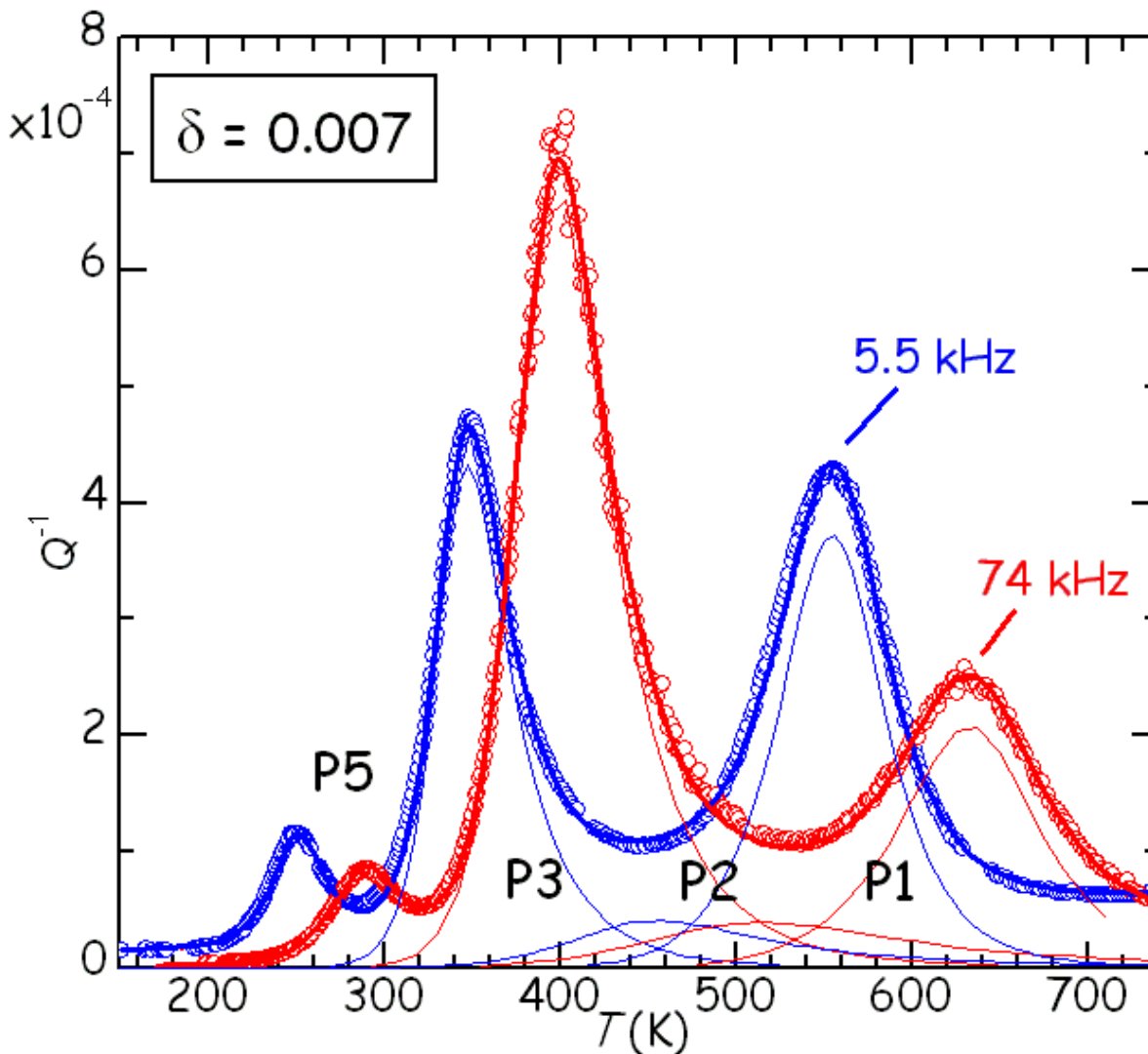
P2 between states differing by $E_2 = W_1 - W_2$:

$$\Delta(T) \propto \frac{c_p}{T \cosh^2(E_2 / 2kT)}$$

$$\tau^{-1} = \tau_0^{-1} \exp(-W_2 / kT) \cosh(E_2 / 2kT)$$

routines for calculating μ , concentrations, and Q^{-1} peaks written in Origin C and integrated in the non linear fitting tool

Fit



binding energies

$$E_p = 0.184 \text{ eV}$$

$$E_c = 0.26 \text{ eV}$$

free isolated V_O (P_F)

$$c = c_F$$

$$W_F = 0.60 \pm 0.007 \text{ eV}$$

$$\tau_{0F} = (5 \pm 1) \times 10^{-14} \text{ s}$$

$$\alpha \geq 0.95$$

$$(\Delta\lambda)_F = 0.026$$

pair reorientation (P_P)

$$c = c_P$$

$$W_P = 0.97 \pm 0.04 \text{ eV}$$

$$\tau_{0P} = (7 \pm 4) \times 10^{-14} \text{ s}$$

$$\alpha \geq 0.95$$

$$(\Delta\lambda)_P = 1.87 \times (\Delta\lambda)_F$$

intermediate (P_I)

$$c = c_P$$

$$W_P \sim 0.86 \text{ eV}$$

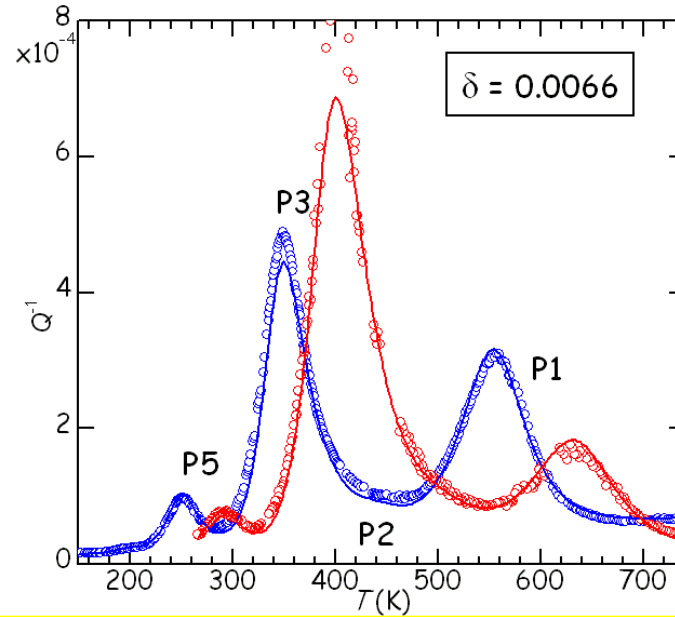
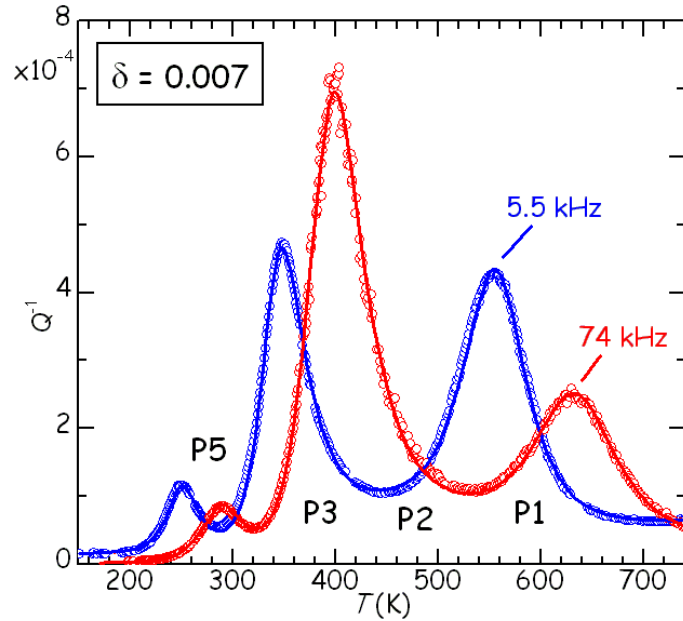
$$\alpha \sim 0.35$$

$$(\Delta\lambda)_P = 5 \times (\Delta\lambda)_F$$

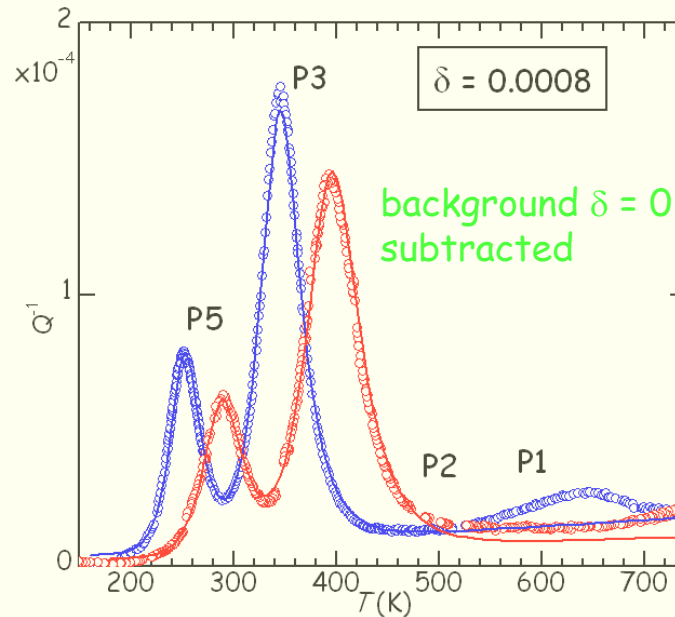
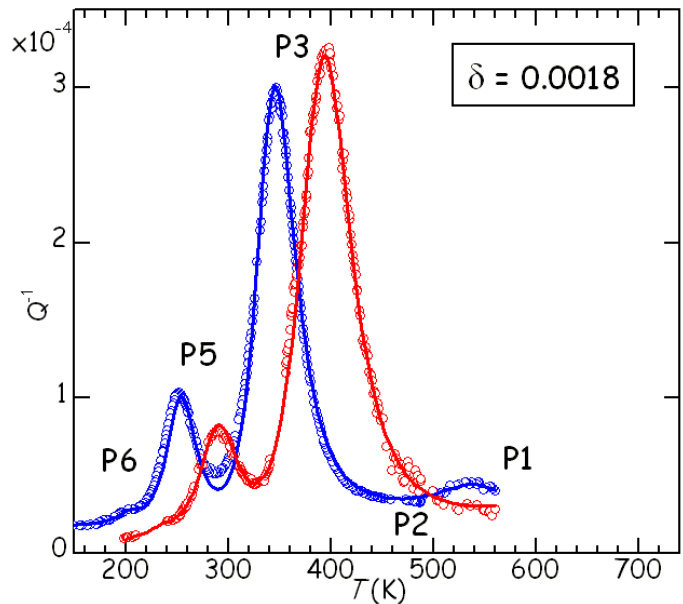
same parameters
for all $\delta > 0.001$!

other configurations
contribute to P2:
 $c > c_P$ and $(\Delta\lambda)_P \sim (\Delta\lambda)_F$

Fit



same parameters
for all $\delta > 0.001$



$\delta = 0.00064$
instead of 0.0008
estimated from T_C

$E_p = 0.1$ eV instead
of 0.18 eV

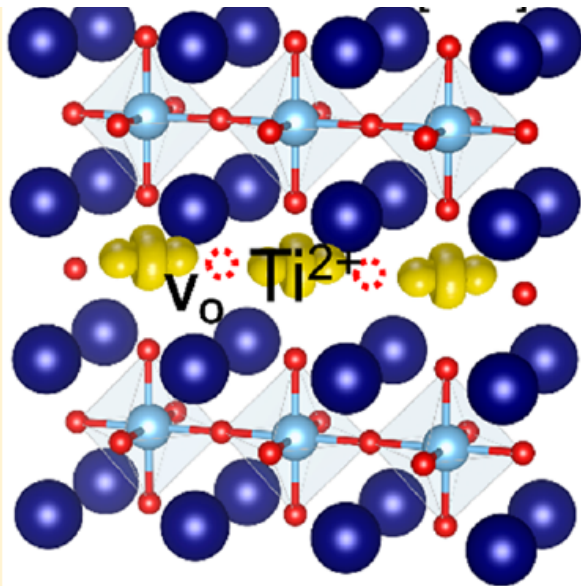
Confirmations from other recent experiments: V_O pairs

Highly O deficient SrTiO_3 films obtained by PLD at low p_{O_2}

V_O - Ti^{2+} - V_O pairs

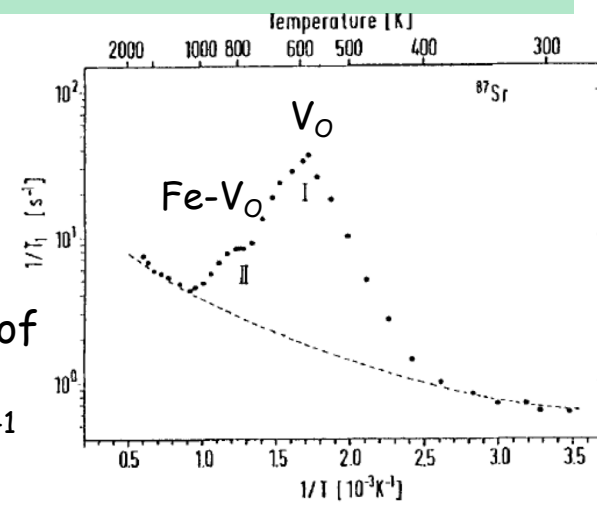
diffuse X-ray scattering: linear defects

Photoemission spectroscopy : Ti^{2+}



Eom *et al.* "Oxygen Vacancy Linear Clustering in a Perovskite Oxide"
J. Phys. Chem. Lett. 8, 3500 (2017)

Confirmations from other studies: hopping barrier of V_O

Method		$\Delta H_{\text{mig}, V}$ (eV)	
Isotope diffusion		0.6	Metlenko, De Souza, Park and Weirich "Behavior of oxygen vacancies in single-crystal SrTiO ₃ : Equilibrium distribution and diffusion kinetics" Phys. Rev. B 85, 174109 (2012)
Isotope exchange		1.13	
Chemical diffusion		0.98	
Chemical diffusion		0.3	Schwarz and Anderson, J. Electrochem. Soc. 122, 707 (1975)
Isotope exchange		1.06	
Chemical diffusion	$\delta < 5 \times 10^{-4}$	0.65	
Chemical diffusion		2.1	Hackmann and Kanert, Radiat. Eff. Defects Solids, 119-121, 651 (1991)
Electrical conductivity		1.0	
Nuclear-spin relaxation		0.62	
Electrical conductivity		0.86	Cordero, Phys. Rev. B 76, 172106 (2007)
Anelastic relaxation	paired	0.98	
Anelastic relaxation	isolated	0.60	
Electrical conductivity		1.4	NSR rate $1/T_1$ of the nuclei is analogous to Q^{-1} 
Thermally stimulated relaxation		0.91	
C: Empirical pair potentials		0.65	
C: Empirical pair potentials		0.76	
C: Density functional theory		0.4 – 0.7	
C: Empirical pair potentials		0.9	
C: Density functional theory		0.6	
C: Density functional theory		0.6	
C: Density functional theory		0.6	
C: Empirical pair potentials		0.96 – 1.35	

Confirmations from other studies: hopping barrier of V_O

V. Metlenko, ... , R. Waser, R. De Souza, *Nanoscale* 6, 12864 (2014)

	$\Delta H_{\text{mig}, V_O} / \text{eV}$	Ref.
EPP calculations	0.63	This study
DFT calculations	0.53	43
DFT calculations	0.51	44
DFT calculations	0.58	45
Isotope diffusion	0.62 ± 0.08	29
Nuclear spin relaxation	0.62	46
Anelastic relaxation	0.60 ± 0.007	47
Chemical diffusion	0.65 ± 0.06	48

43 Walsh *et al.*, *Phys. Rev. B* 83 220301 (2011)

44 T. Mizoguchi *et al.* *Appl. Phys. Lett.* 98, 091909 (2011)

45 M. Lontsi-Fomena *et al.* *Comput. Mater. Sci.* 44, 53 (2008)

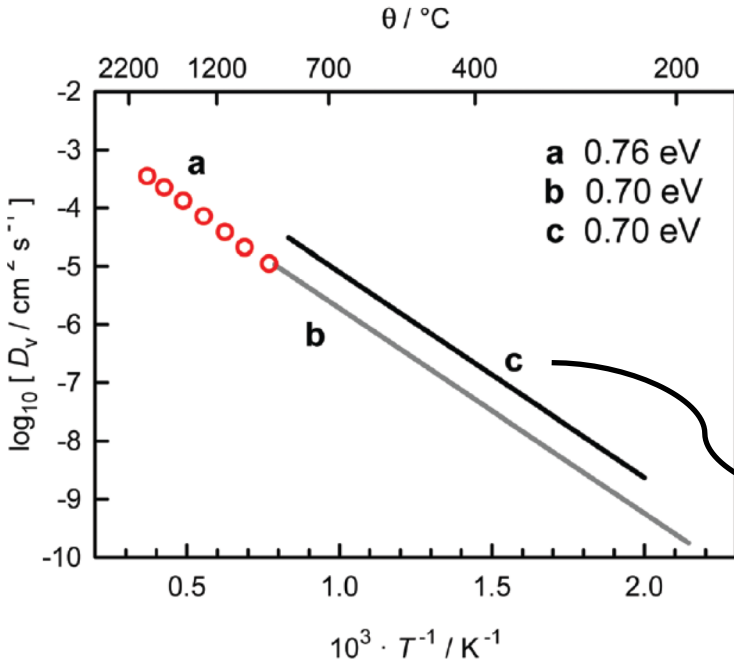
46 Hackmann and Kanert, *Radiat. Eff. Defects Solids*, 119-121, 651 (1991) NMR

47 F. Cordero, *Phys. Rev. B* 76, 172106 (2007) anelastic

48 Schwarz and Anderson, *J. Electrochem. Soc.* 122, 707 (1975) $\delta < 5 \times 10^{-4}$

Most reliable studies on the hopping of V_O in $BaTiO_3$

J. Kaub, J. Kler, S. C. Parker and R. A. De Souza, *Phys. Chem. Chem. Phys.* 22, 5413 (2020)



activation enthalpy of migration of V_O in $BaTiO_3$ from

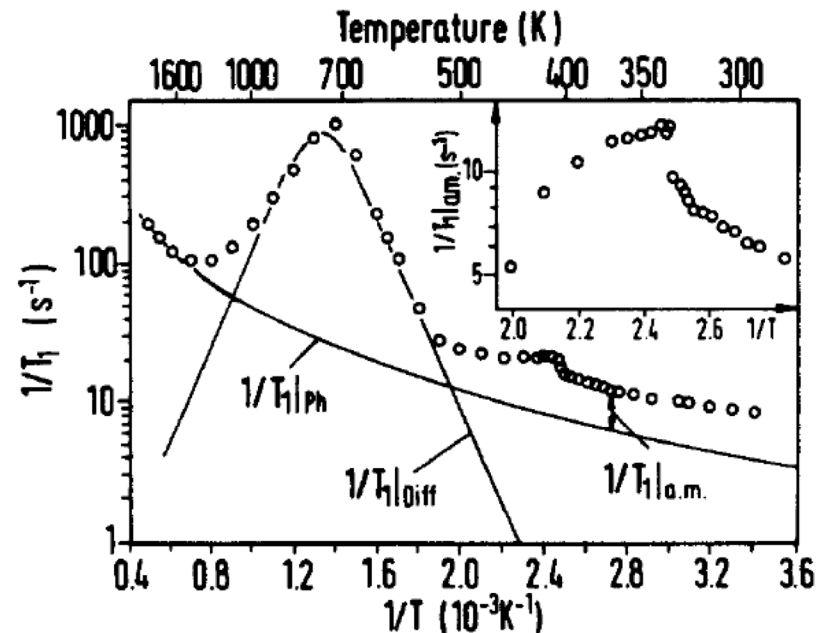
- a) isotope exchange: 0.70 eV
- b) molecular dynamics simulations: 0.76 eV
- c) NMR: 0.70 eV

Kanert *et al.* *Solid State Commun.* 91, 465 (1994)

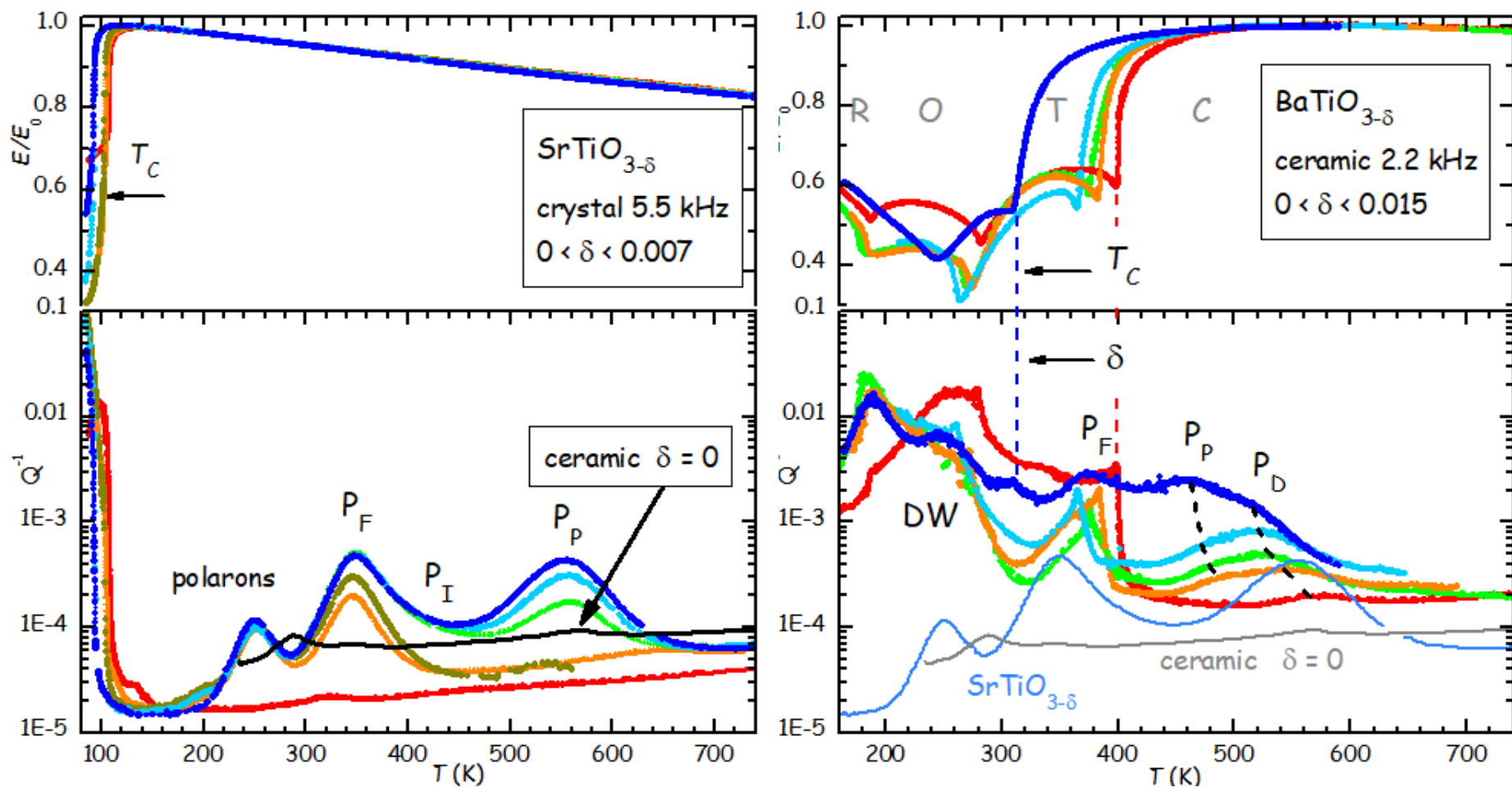
Maier and Randall

J. Am. Ceram. Soc. 99, 3360 (2016)

impedance spectroscopy: 0.70 eV

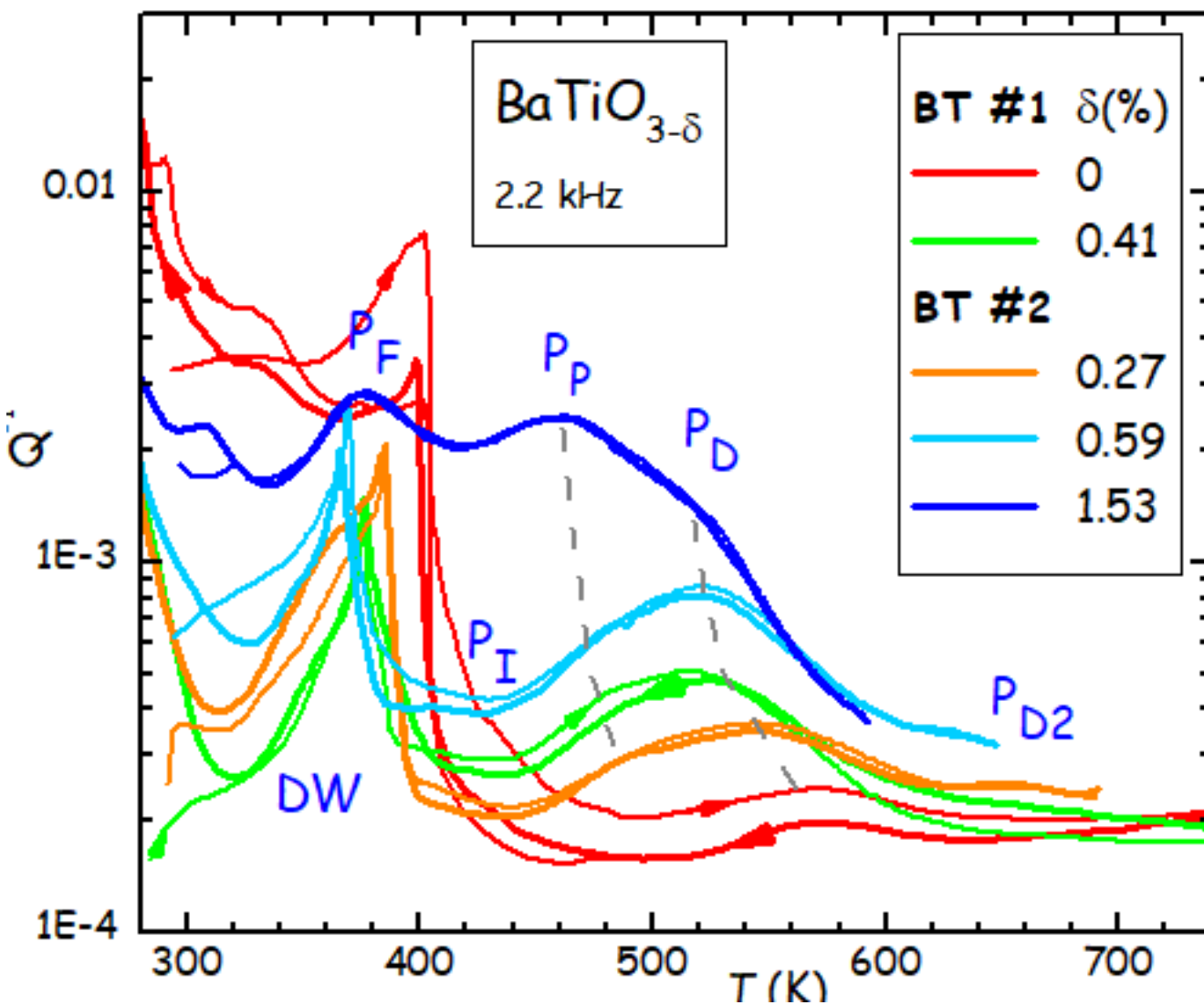


Anelastic spectra of $\text{BaTiO}_{3-\delta}$ vs $\text{SrTiO}_{3-\delta}$



- precursor softening due to phase transitions (deviation from stiffening linear with T) already below 800 K
- higher background dissipation ceramic vs single crystal?)
- T_C decreases with O deficiency until at $\delta = 0.017$ also P_F from isolated V_O is visible
- increasing δ all the thermally activated peaks increase the intensity and shift to lower T

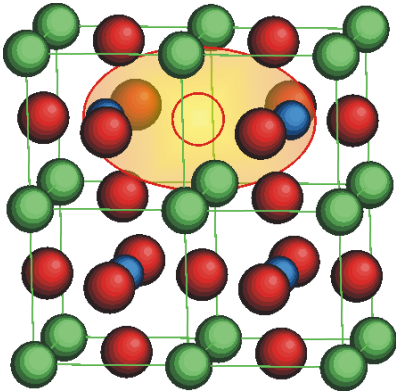
Stability of the anelastic spectrum of $\text{BaTiO}_{3-\delta}$



thin splines = heat
thick splines = cool

Fitting functions

hopping of very diluted isolated V_O in ceramic:
orientational average of Debye relaxation



each peak fitted with

used to estimate $\Delta\lambda$

$$Q^{-1} = \underbrace{\frac{2}{15} \frac{c v_0 E}{k_B T}}_{\Delta / T} (\Delta\lambda)^2 \frac{\omega\tau}{1 + (\omega\tau)^2}$$

$$Q^{-1} = \frac{\Delta}{T} \frac{\alpha(\omega\tau)^\alpha}{1 + (\omega\tau)^{2\alpha}}$$

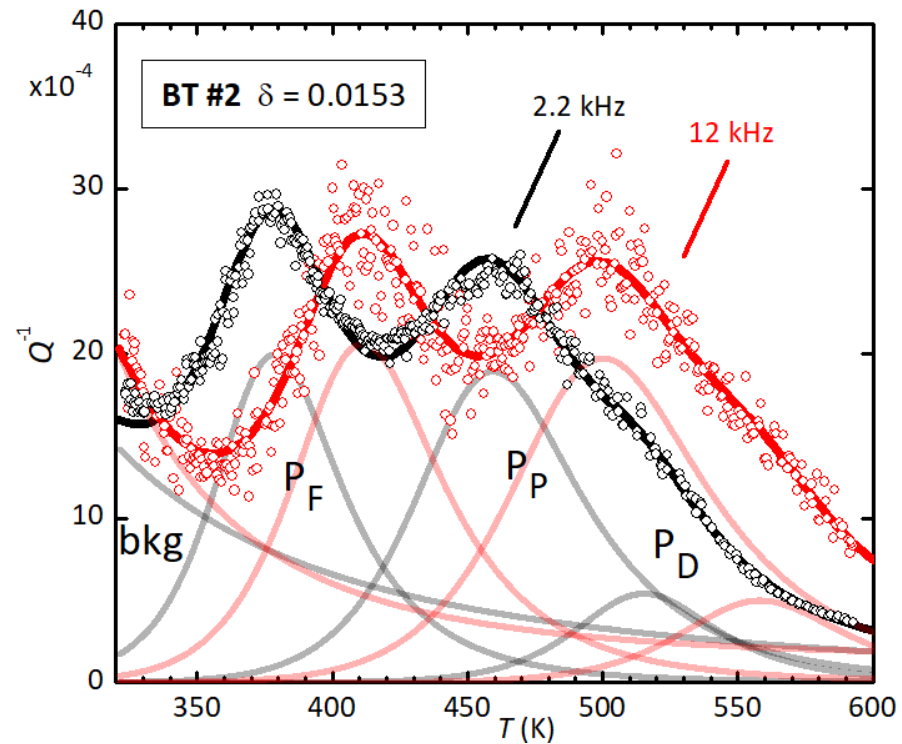
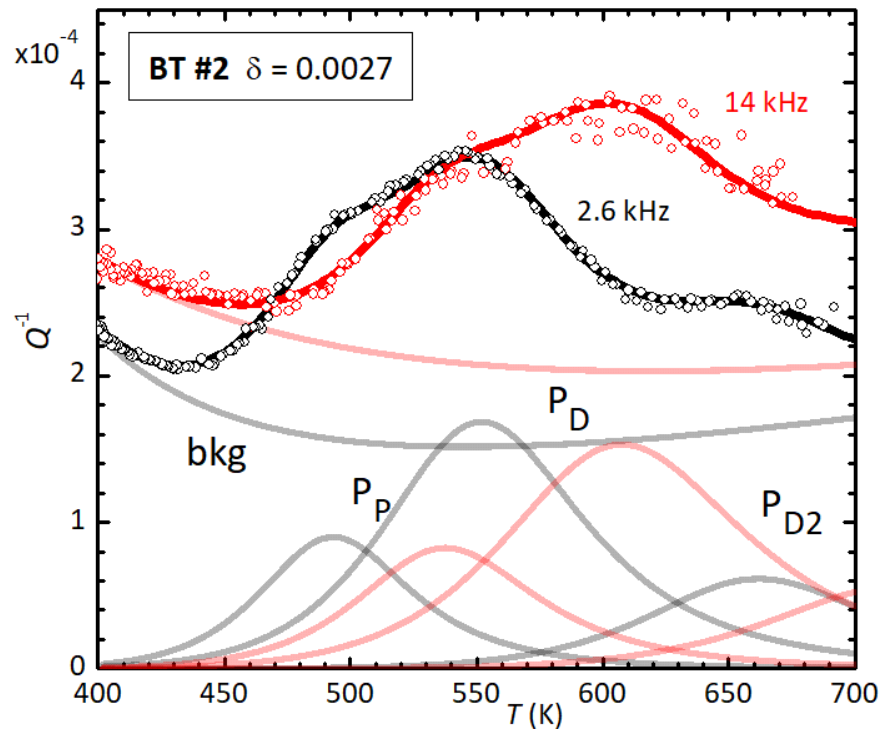
$\alpha \leq 1$ Fuoss-Kirkwood broadening

$$\Delta(T) \rightarrow \frac{\Delta}{T \cosh^2(A/2kT)}$$

$$\tau^{-1} = \tau_0^{-1} \exp(-W/kT) \cosh(A/2kT)$$

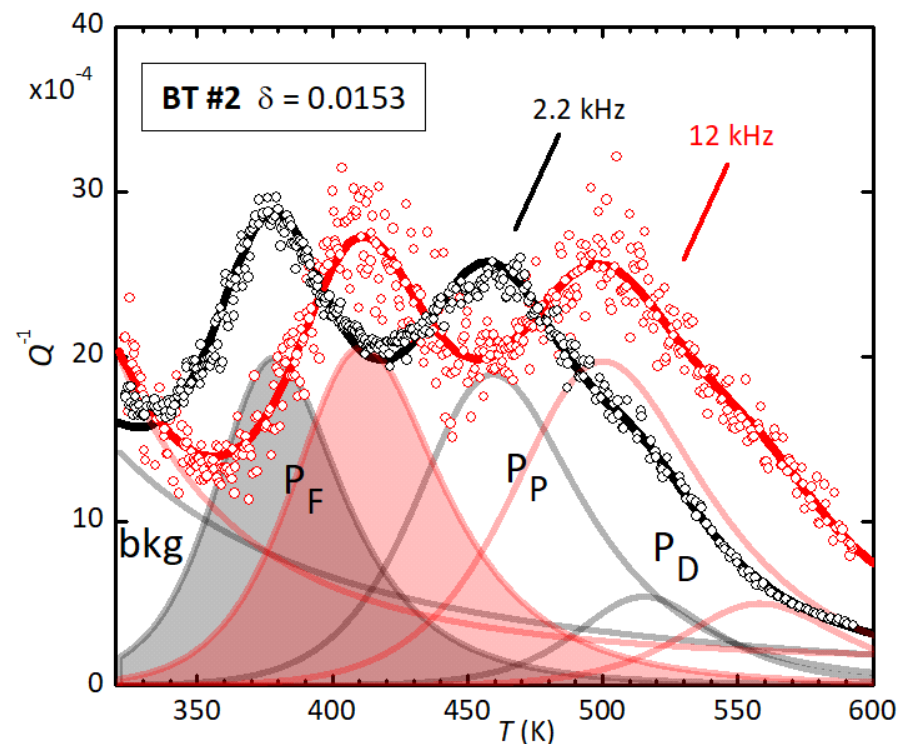
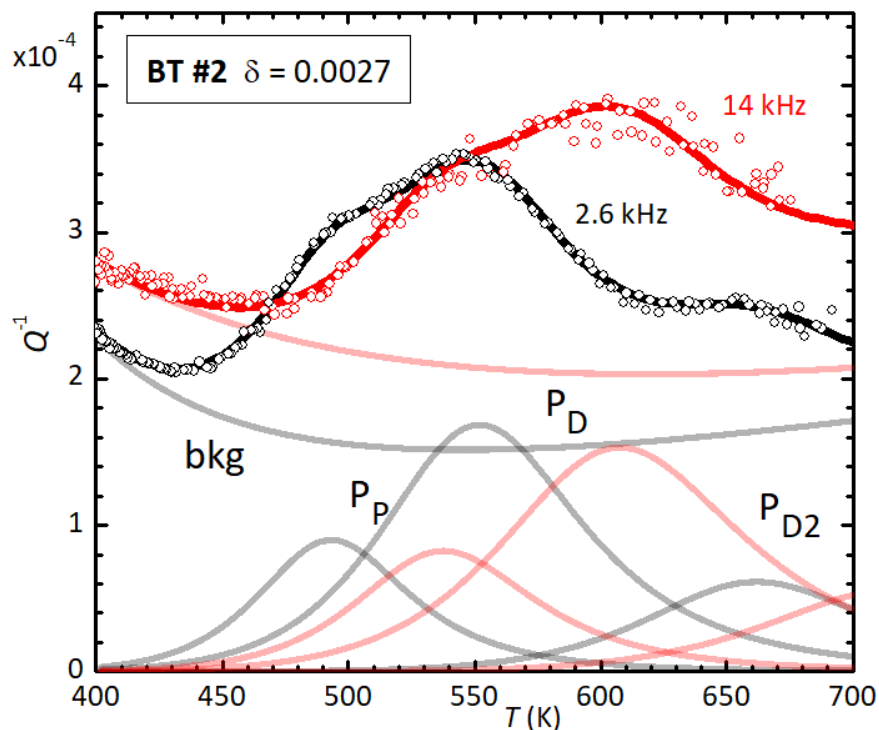
relaxation between states with
energies differing of A

Fits of the anelastic spectra of $\text{BaTiO}_{3-\delta}$



- P_F : hopping of free V_O
- P_P : reorientation of V_O pair
- P_D : $(V_{Ba}/Ti/impurity)-V_O$ pair
- P_{D2} : other $(V_{Ba}/Ti/impurity)-V_O$ pair

P_F : hopping of free V_O



NMR: Kanert *et al.*, Solid State Commun. 91, 465 (1994);

Impedance spectr.: Maier and Randall, J. Am. Ceram. Soc. 99, 3360 (2016);

Isotope exchange: J. Kaub *et al.*, Phys. Chem. Chem. Phys. 22, 5413 (2020)

V_O migration in $BaTiO_3$: $W = 0.70$ eV

$\delta = 0.0153$

$W = 0.72$ eV

$\tau_0 = 2.6 \times 10^{-14}$ s

$\alpha = 0.84$

$A/k_B = 7.4$ K ~ 0

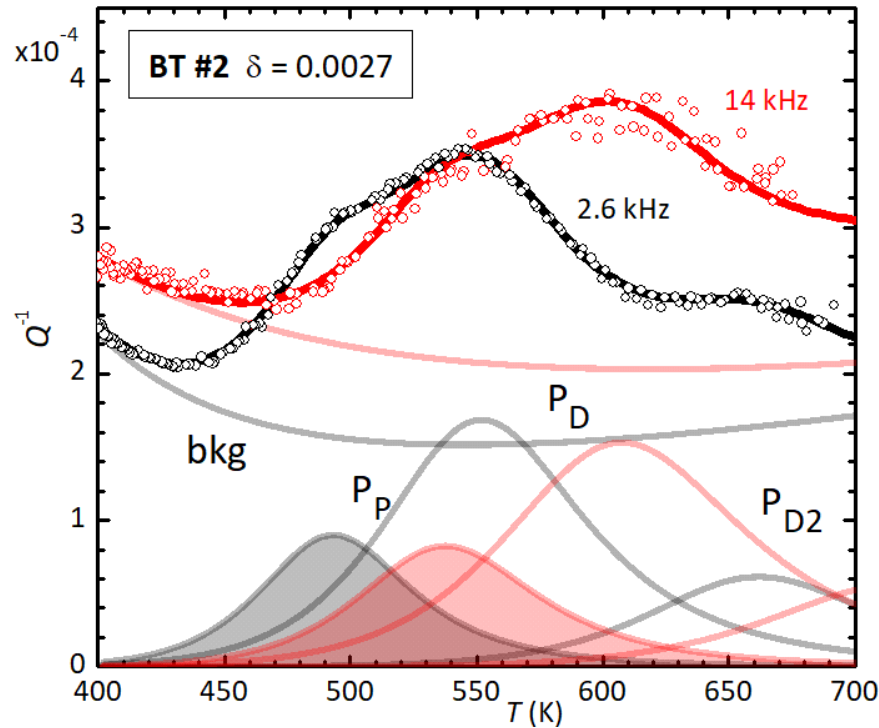
$\Delta = 3.51$ K $\rightarrow \Delta\lambda = 0.077$

($SrTiO_3$: 0.60 eV)
point defect

} single Debye

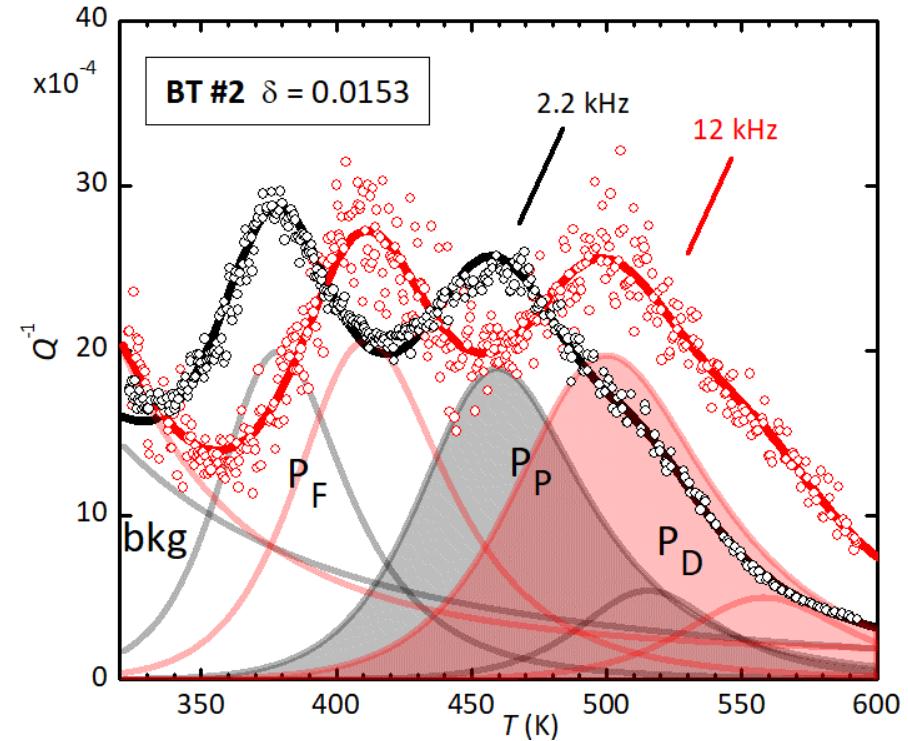
($SrTiO_3$: 0.026)

P_P : reorientation of V_O pair



$W = 0.87 \text{ eV}$
 $\tau_0 = 9.0 \times 10^{-14} \text{ s}$
 $\alpha = 0.91$
 $A/k_B = 0 \text{ K}$
 $\Delta = 0.0888 \text{ K}$

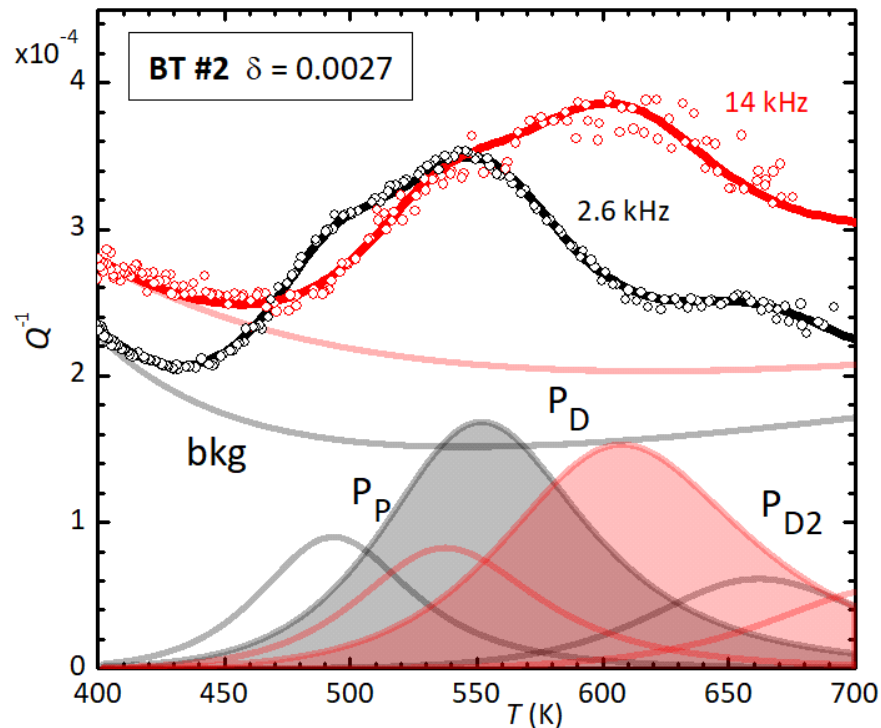
$(\text{SrTiO}_3: 0.97 \text{ eV})$
 point defect



$W = 0.85 \text{ eV}$
 $\tau_0 = 4.7 \times 10^{-14} \text{ s}$
 $\alpha = 0.80$
 $A/k_B = 940 \text{ K}$
 $\Delta = 4.29 \text{ K}$

$$\frac{\Delta(\delta=0.0153)}{\Delta(\delta=0.0027)} = 48 = 1.5 \times \left(\frac{0.0153}{0.0027} \right)^2$$

P_D : defect- V_O pair



$$W = 0.87 \text{ eV} \quad (\text{SrTiO}_3: 0.97 \text{ eV})$$

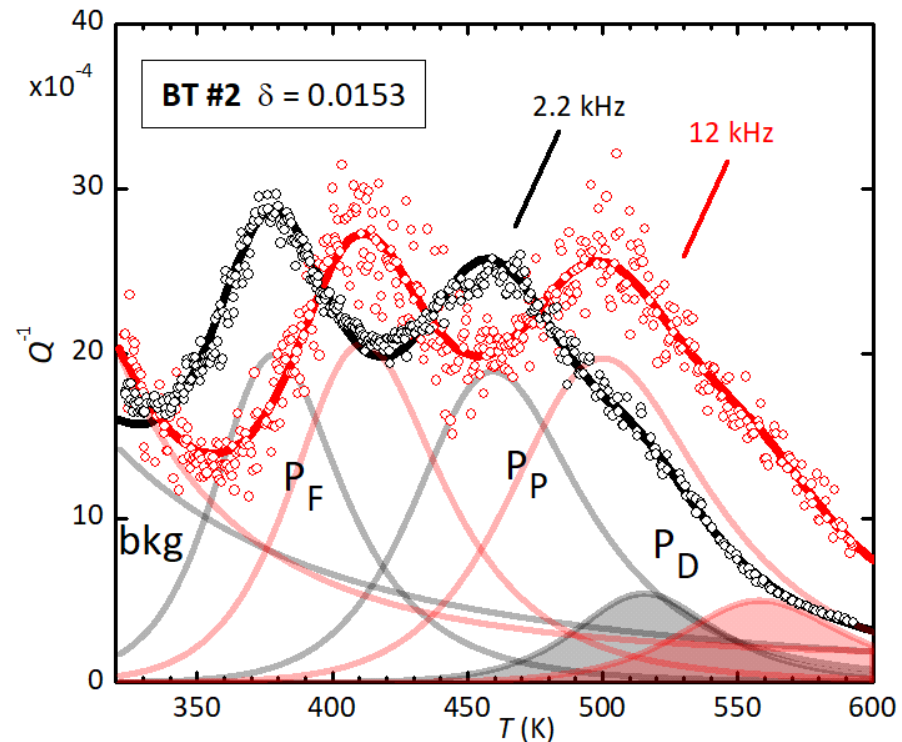
$$\tau_0 = 7.1 \times 10^{-13} \text{ s} \quad \text{point defect}$$

$$\alpha = 1$$

$$A/k_B = 0$$

$$\Delta = 0.186 \text{ K}$$

defect: V_{Ba} or V_{Ti} or acceptor impurity



$$W = 0.97 \text{ eV}$$

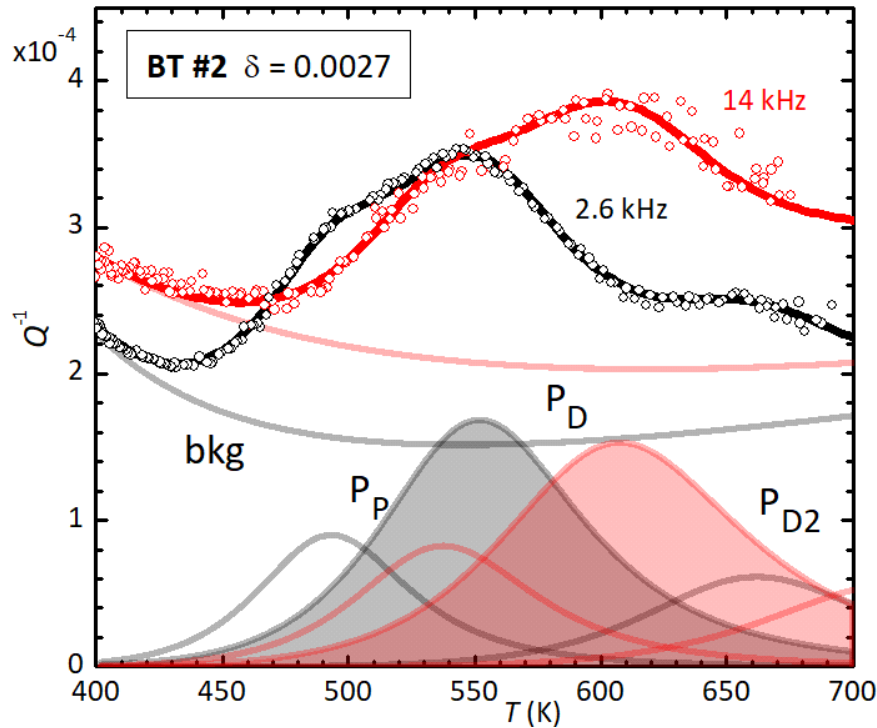
$$\tau_0 = 2.2 \times 10^{-14} \text{ s}$$

$$\alpha = 1$$

$$A/k_B = 0$$

$$\Delta = 0.557 \text{ K}$$

P_D : defect- V_O pair



$$W = 0.87 \text{ eV} \quad (\text{SrTiO}_3: 0.97 \text{ eV})$$

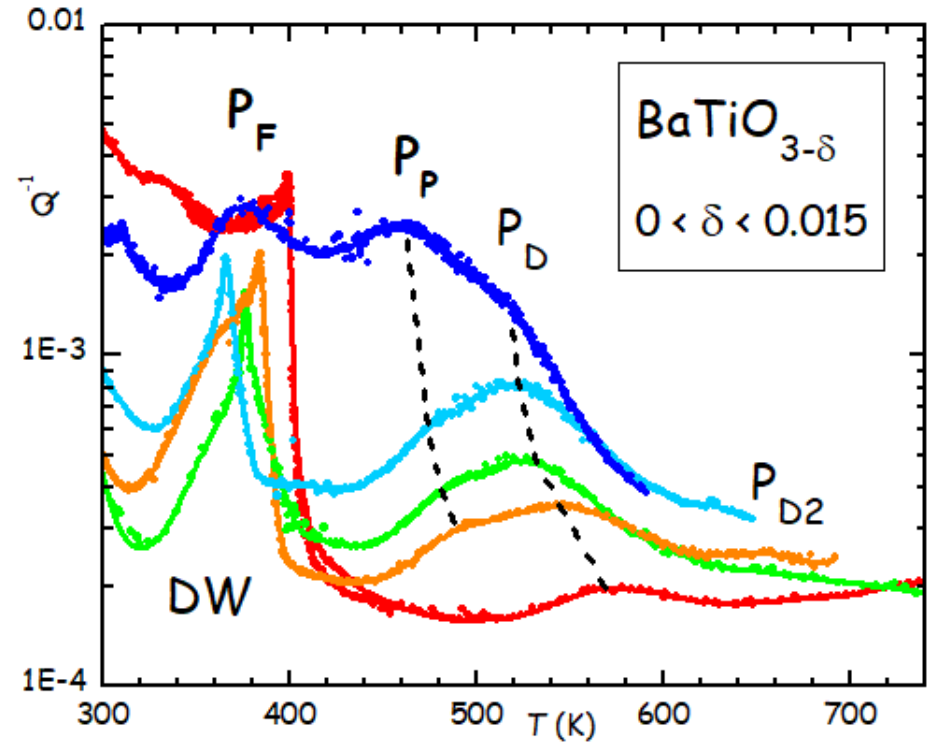
$$\tau_0 = 7.1 \times 10^{-13} \text{ s} \quad \text{point defect}$$

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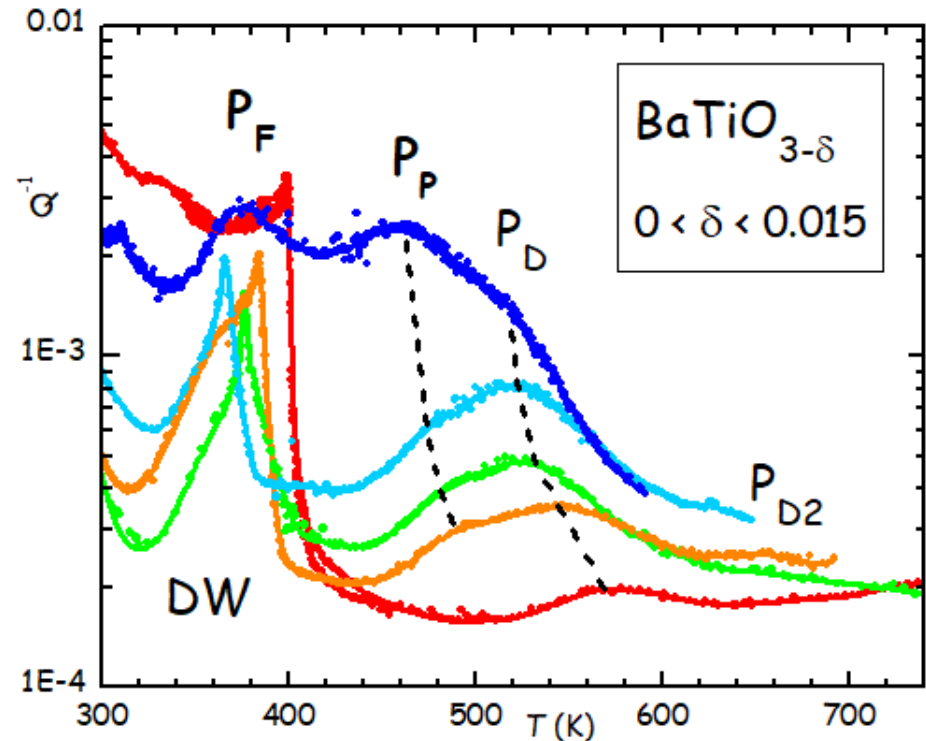
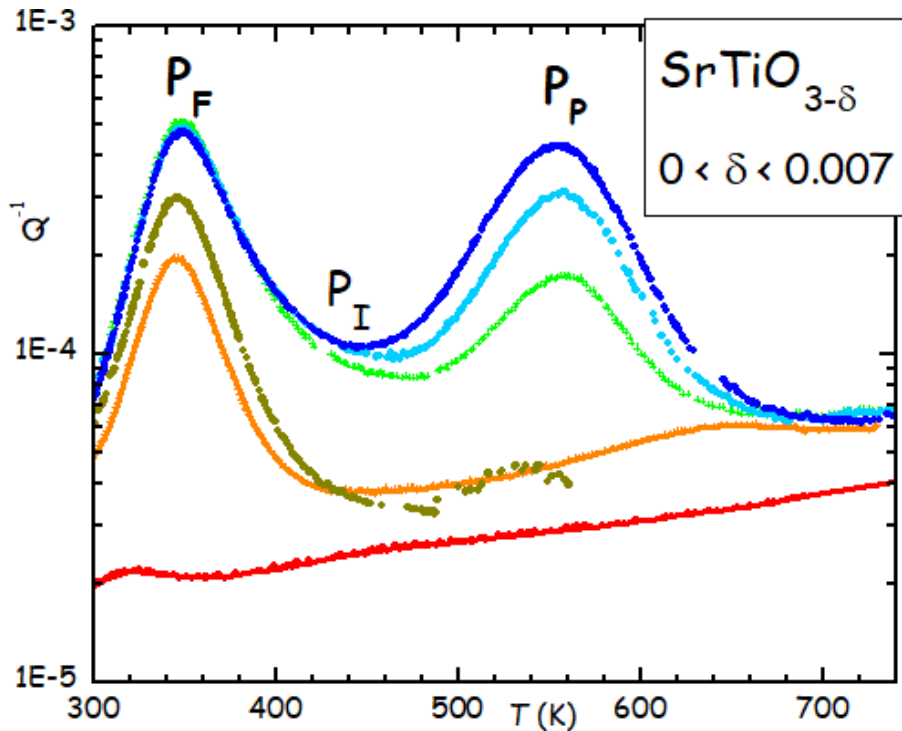
$$\tau_0 = 2.2 \times 10^{-14} \text{ s}$$

$$\alpha = 1$$

$$A/k_B = 0$$

$$\Delta = 0.557 \text{ K}$$

Why the differences between $\text{BaTiO}_{3-\delta}$ and $\text{SrTiO}_{3-\delta}$?

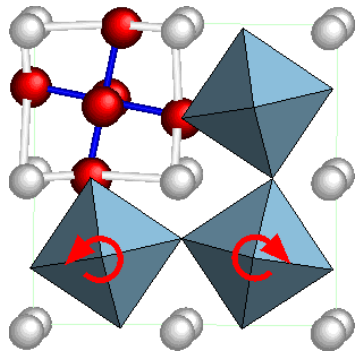


elastic dipole of isolated V_O from the intensity of P_F :
 $\Delta\lambda = 0.026$ $\Delta\lambda = 0.077$

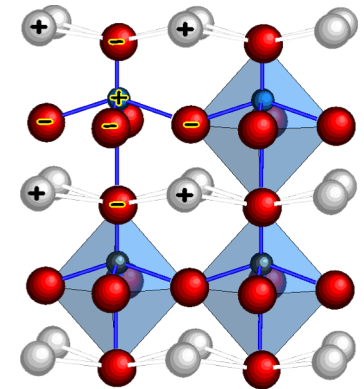
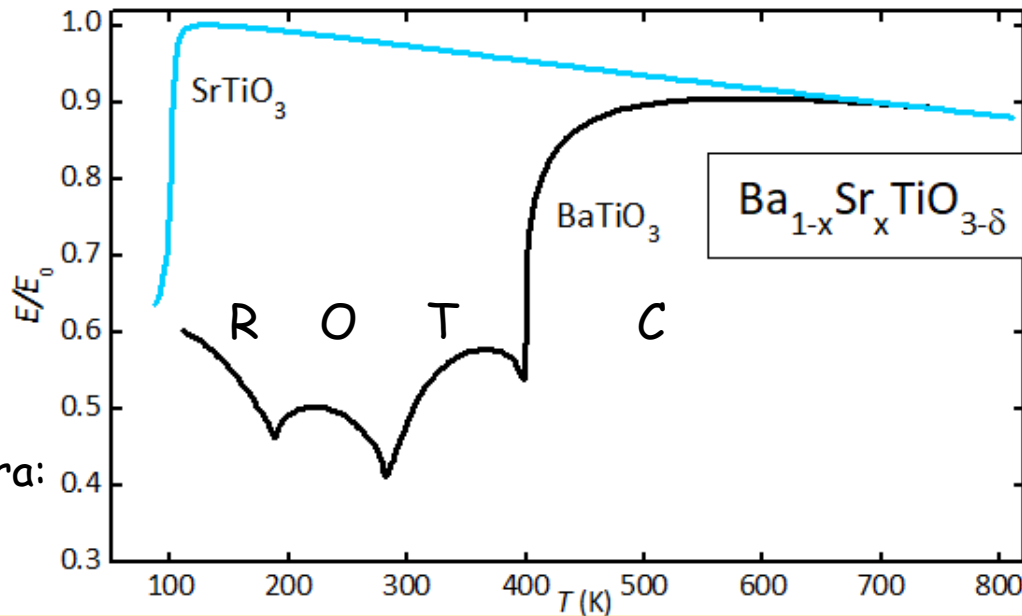
in $\text{BaTiO}_{3-\delta}$

- the peaks shift to lower T with increasing δ
- $\Delta\lambda$ is three times larger

Phase transitions and Young's modulus of $\text{Ba}_{1-x}\text{Sr}_x\text{TiO}_{3-\delta}$



rotation of octahedra:
antiferrodistortive
non-polar



ferroelectric mode
with polarisation P

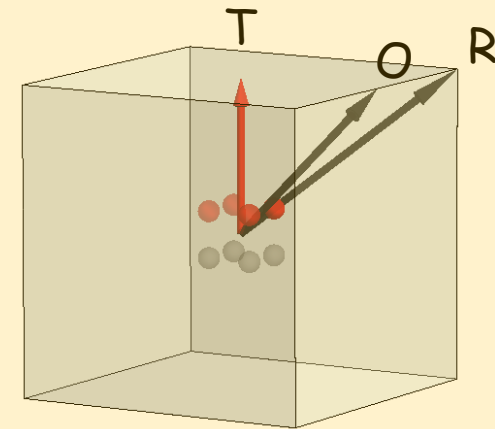
Eight-site model

Mason and Matthias, Phys. Rev. 74 1622 (1948); Devonshire (1949)

...

Bersuker, Phys. Lett. 20, 589 (1966); Chem. Rev. 121, 1463 (2021):
pseudo- Jahn-Teller effect where the electronic energy is
lowered by the increase of covalency between Ti and the closest O
atoms.

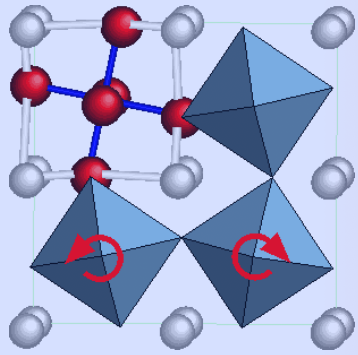
Experimental confirmations: diffuse XRD, EXAFS, NMR, EPR,
Brillouin scattering



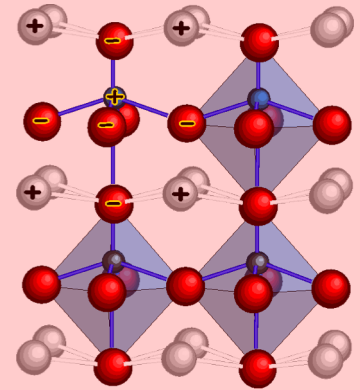
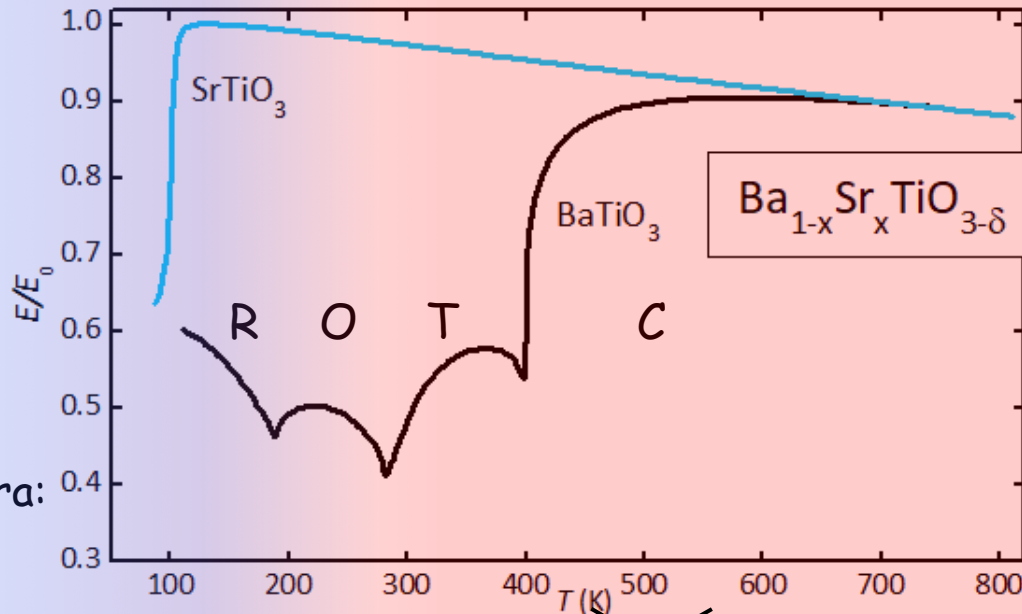
Correlated anharmonic vibrations of Ti

Hüller, Solid State Commun. 7 589 (1969) ...

Softening at the phase transitions



rotation of octahedra:
antiferrodistortive
non-polar



ferroelectric mode
with polarisation P

$$*P^2 + *P^4 \dots * \sigma^2 \dots \cancel{* \sigma P} + * \sigma P^2 + \dots$$

OP = $\phi \sim$ rotation angle

OP = $P \sim$ Ti displacement

$$G = F(\phi) - \frac{1}{2}s_0\sigma^2 - R\sigma\phi^2$$

$$G = F(P) - \frac{1}{2}s_0\sigma^2 - Q\sigma P^2$$

same coupling of stress to OP $\rightarrow$ same elastic anomaly

compliance from
free energy:

$$F = \frac{a}{2}(T - T_C)P^2 + \frac{b}{4}P^4$$

simplest expansion in powers of OP

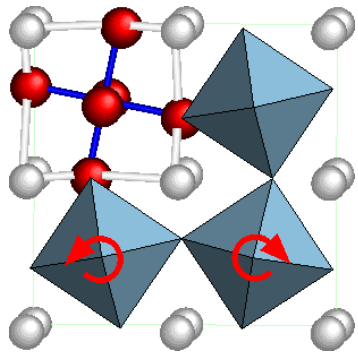
$$E^{-1} = \frac{d\varepsilon}{d\sigma} = -\frac{\partial^2 G}{\partial \sigma^2} + \frac{d\varepsilon}{dP} \frac{dP}{d\sigma} = s_0 + 4\chi Q^2 P^2 = s_0 + 2Q^2/b$$

fluctuations in the cubic phase $4\chi Q^2 \langle P^2 \rangle$

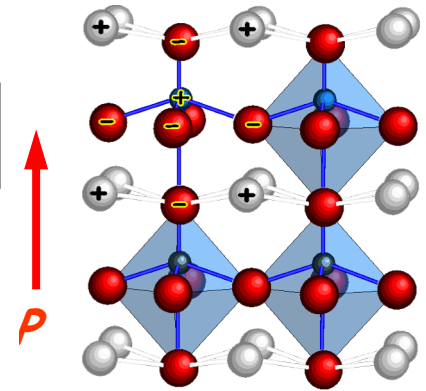
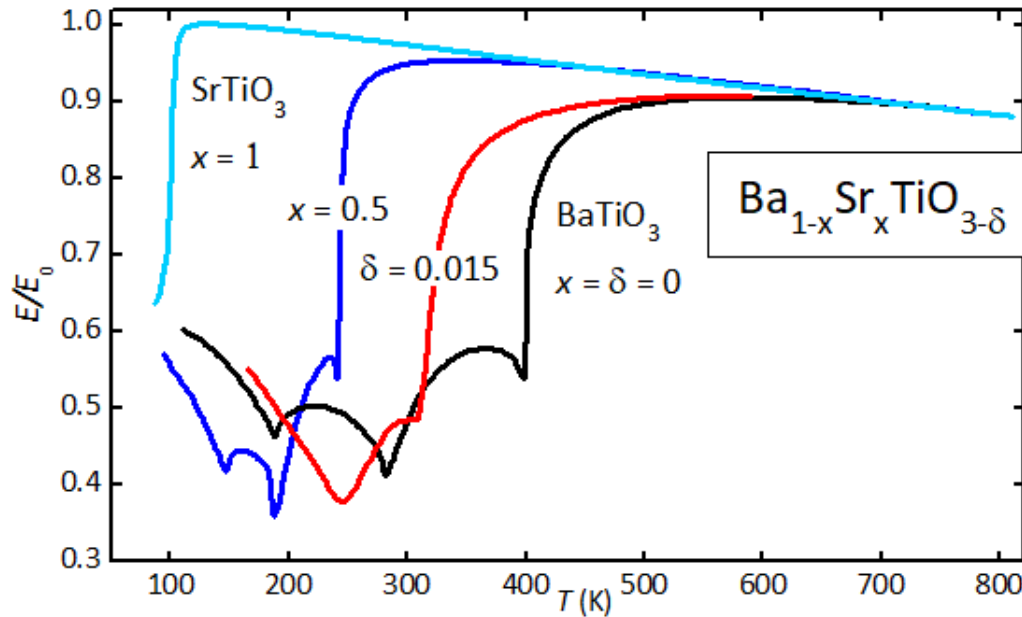
precursor softening

steplike softening at the transition

Phase transitions and Young's modulus of $\text{Ba}_{1-x}\text{Sr}_x\text{TiO}_{3-\delta}$



rotation of octahedra
antiferrodistortive
non-polar



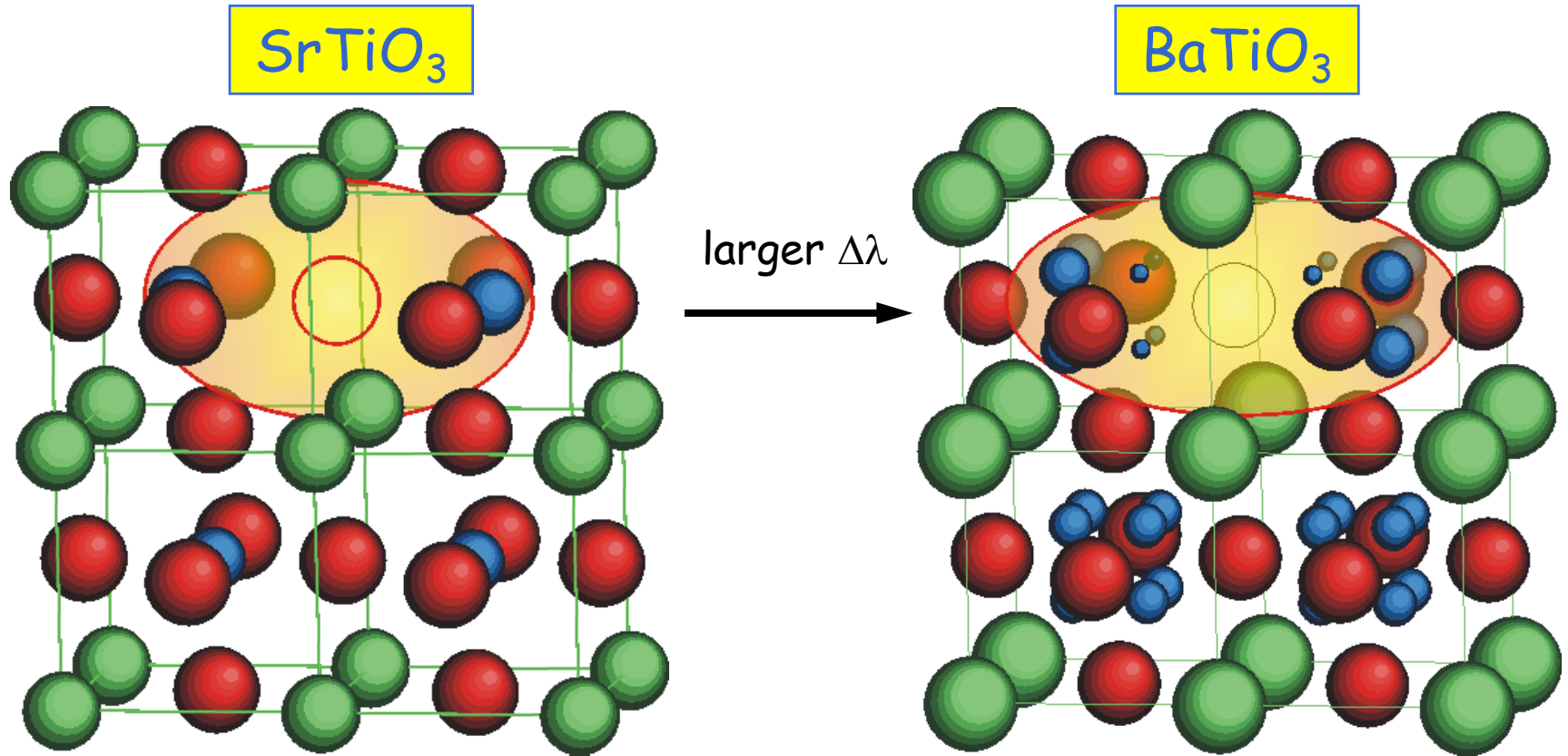
ferroelectric mode
with polarisation P

- Sr is only smaller than Ba but with the same orbitals
- V_O^{2+} is charged and dopes electrons: 1.5% V_O has an effect similar to 25% Sr

volume change of V_O uncertain/small; larger contribution from $\text{Ti}^{4+}/\text{Ti}^{3+}$
polaronic conductivity, low T anelastic relaxations in $\text{SrTiO}_{3-\delta}$

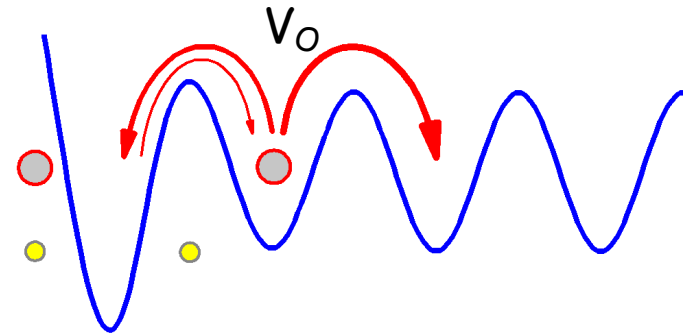
Magnitude of the elastic dipole of V_O

Major contribution to the anisotropy $\Delta\lambda$: the positively charged V_O pushes outwards the nn Ti^{4+} atoms. Easier in $BaTiO_3$

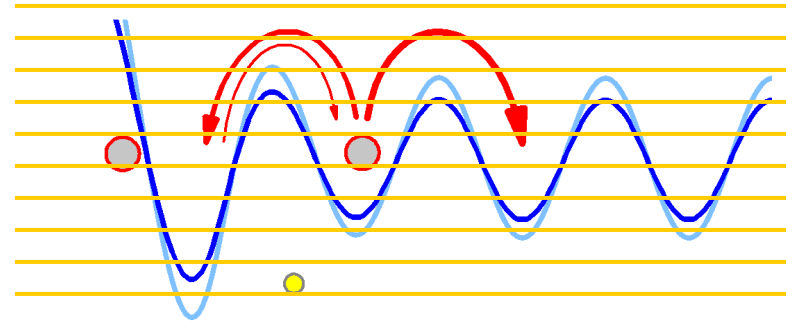


In $BaTiO_3$ the nn Ti atoms will populate the outward off-centre sites, increasing their outward displacement

Decrease of activation energies with doping

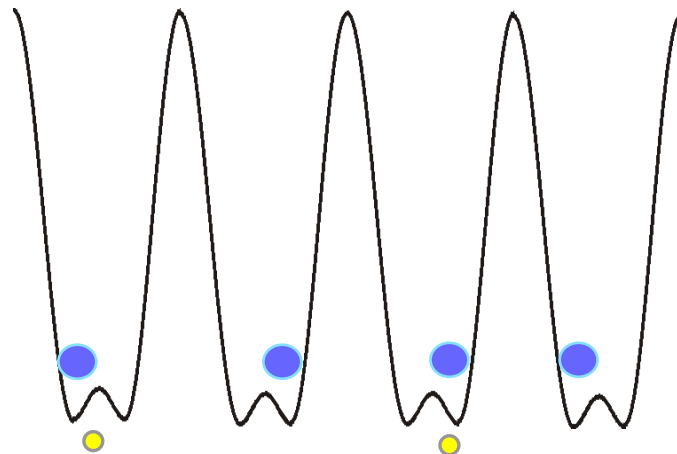


small polaron

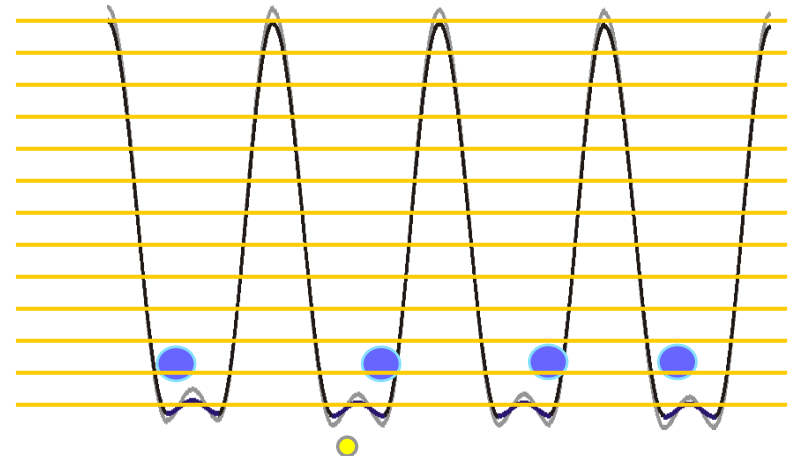


small polaron + band

the potential is washed out by screening $\rightarrow$ smaller barriers (also in SrTiO_3)



8 site potential for Ti



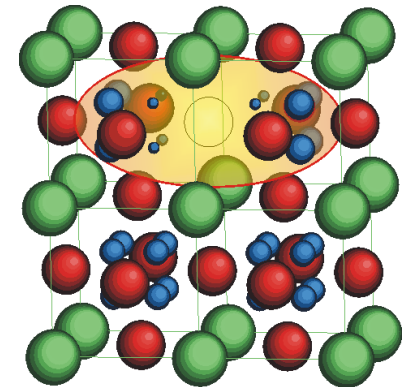
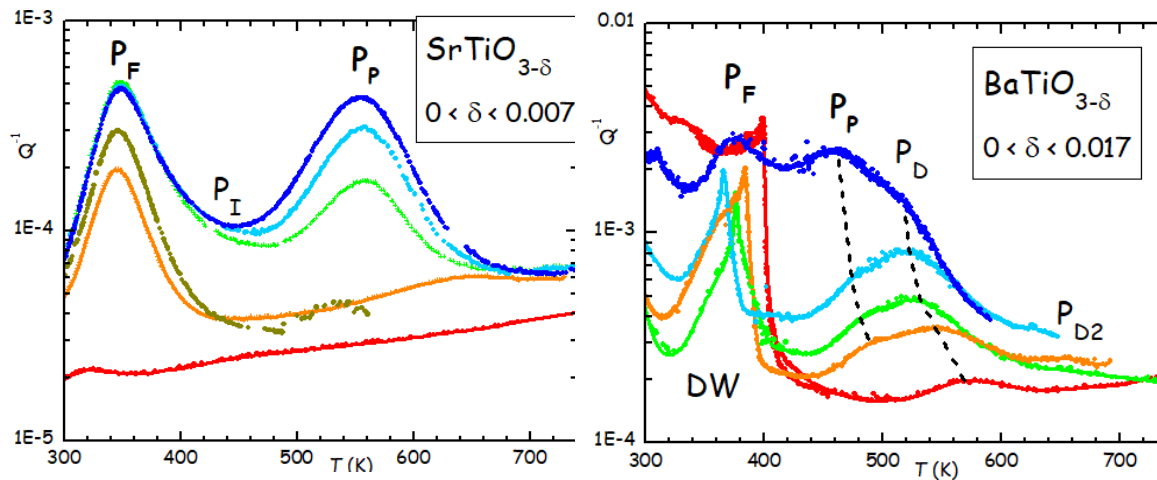
larger effect on the small barriers for Ti off-centre hopping, responsible for the lowering of T_c

- Ti off-centering in undoped $\text{BaTiO}_3 \rightarrow$ larger relaxation around $V_0 \rightarrow$ larger barrier and $\Delta\lambda$
- doping reduces off-centering and all these effects

Conclusions

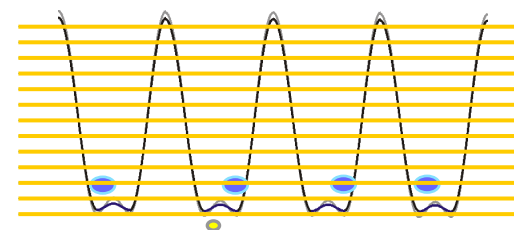
The anelastic spectra of $\text{BaTiO}_{3-\delta}$ contain the same peaks due to isolated and paired V_O as $\text{SrTiO}_{3-\delta}$ but

- the spectra shift much to lower T with increasing δ
- $\Delta\lambda$ of the isolated V_O is three times larger than in $\text{SrTiO}_{3-\delta}$
- the activation energy for single V_O hopping is
- the hopping barrier is 0.70 eV compared to 0.60 eV in $\text{SrTiO}_{3-\delta}$

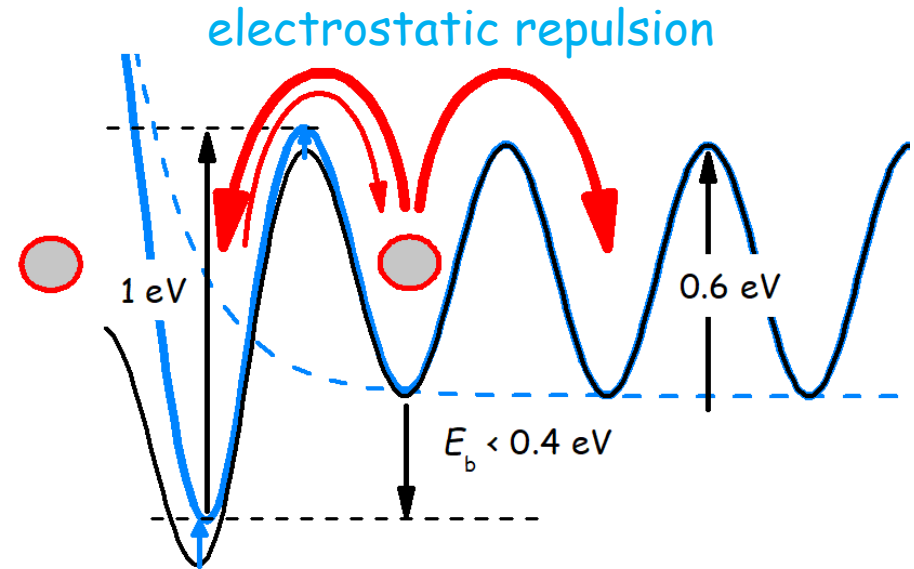
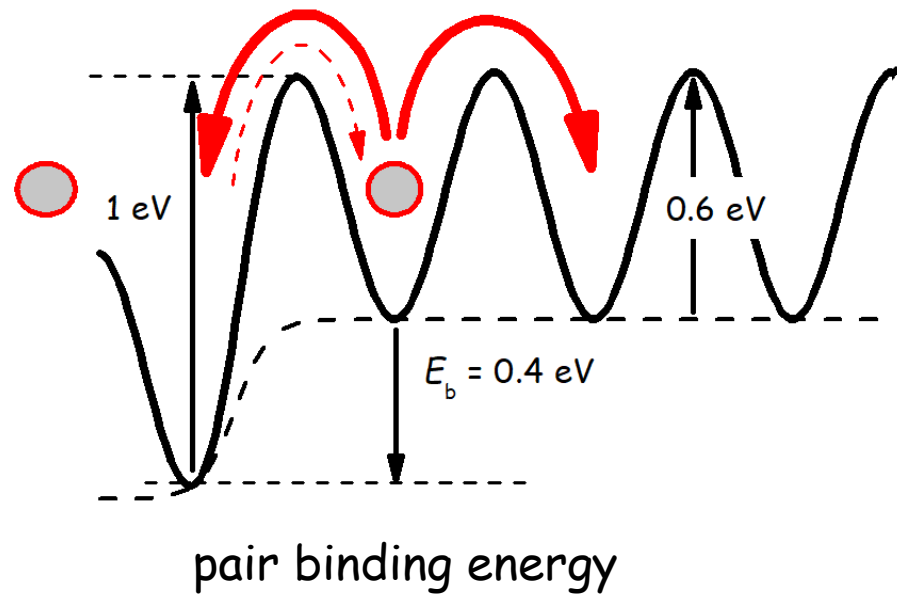


explanation in terms of 8 site potential of off-centre Ti, which

- enhances the outwards shifts of Ti from the V_O
- is washed out by the band electrons doped by V_O



Electrostatic repulsion between V_O and formation of pairs



Boltzmann factor $\exp(E_b/k_B T)$
at 400 K = 10^5 !
all V_O paired at 400 K
P1 could not be observed